



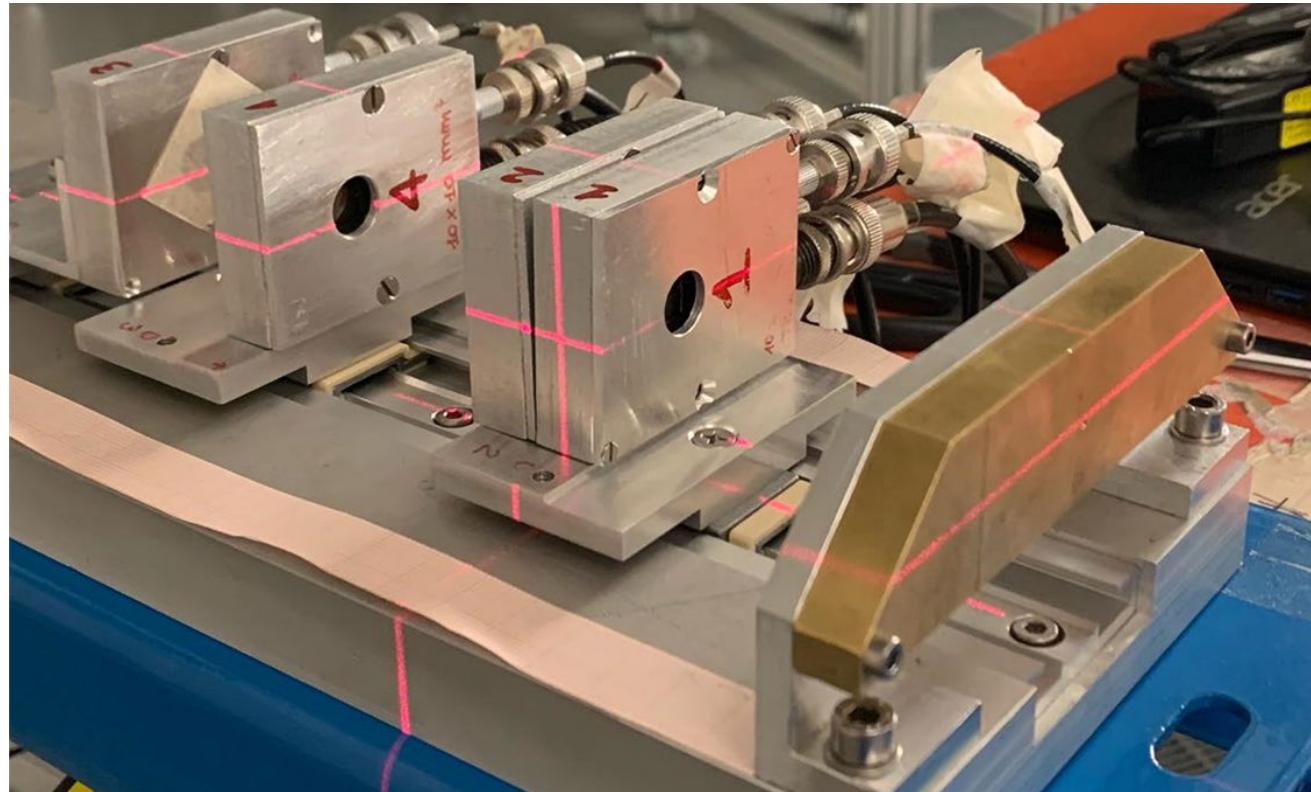
# IMPULSE



Università  
di Catania



IMPULSE has received funding from the European Union's Horizon 2020 research and innovation programme under grant agreement No 871161.



## PRAGUE

### Proton RAnGe measure Using silicon carbidE

Experimental tests and future developments

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# Outline

- | ➤ The project
- | ➤ Detector prototype
- | ➤ Final configuration



# The project

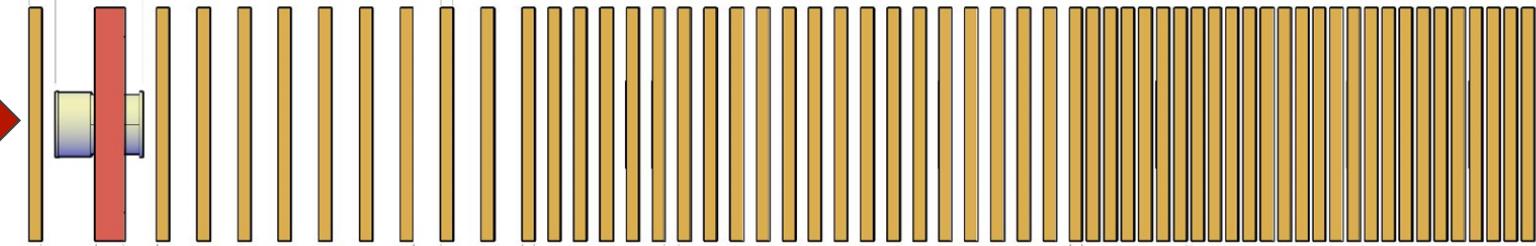
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## (Proton RAnGe measure Using silicon carbidE) detector

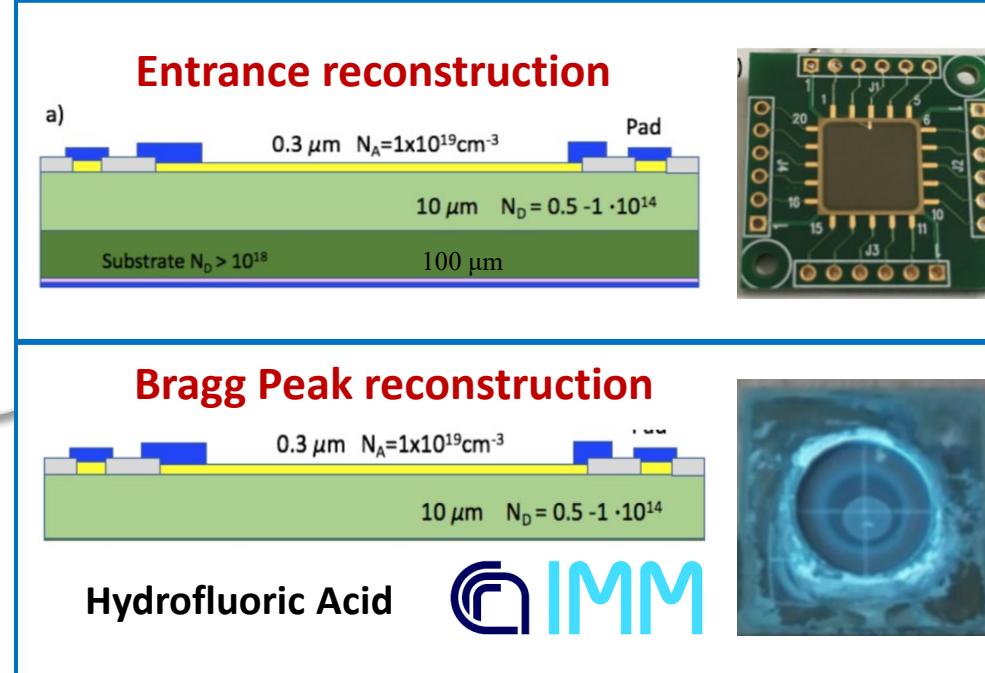
- Online dosimeter;
- PDD distribution of proton beams;
- $10^5 - 10^{10}$  pps intensity beams;
- High longitudinal spatial resolution;
- Dose on biological samples.
- Dose rate independent;
- LET independent;
- High radiation hardness.

Main goal:

Proton beam  
30-150 MeV



PRELIMINARY CONFIGURATION



IMPULSE  
  
**INFN**  
**ei** |   
 beamlines  
  
 MARIE CURIE ACTIONS



30 standard SiC with 10μm of active layer and 100μm of passive substrate

30 new SiC w/o passive layer

Financial support by both INFN and Horizon 2020 and is currently ongoing



**Old generation:**  

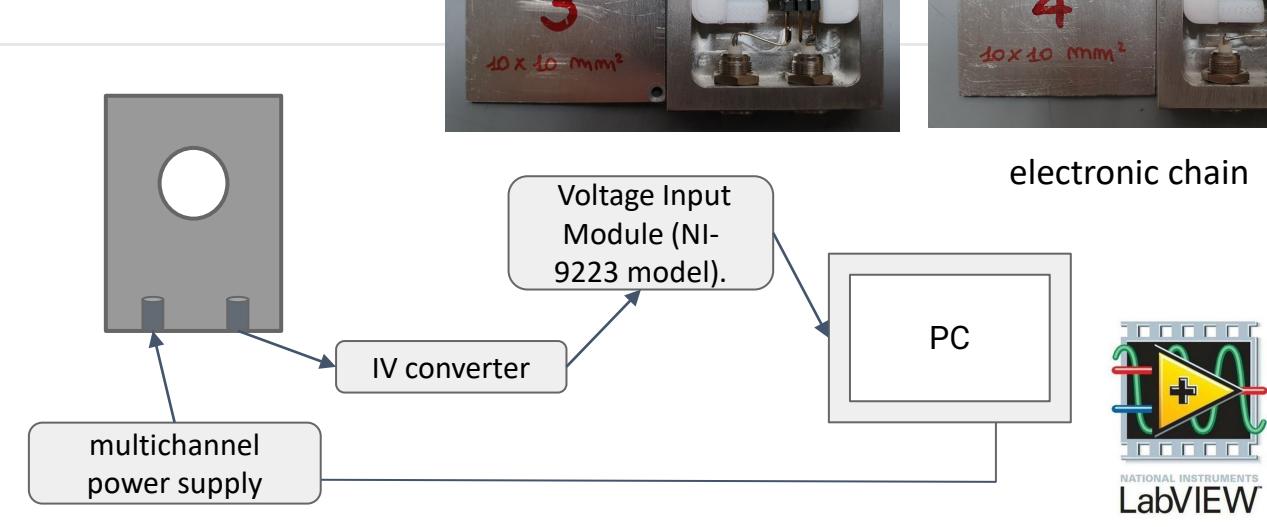
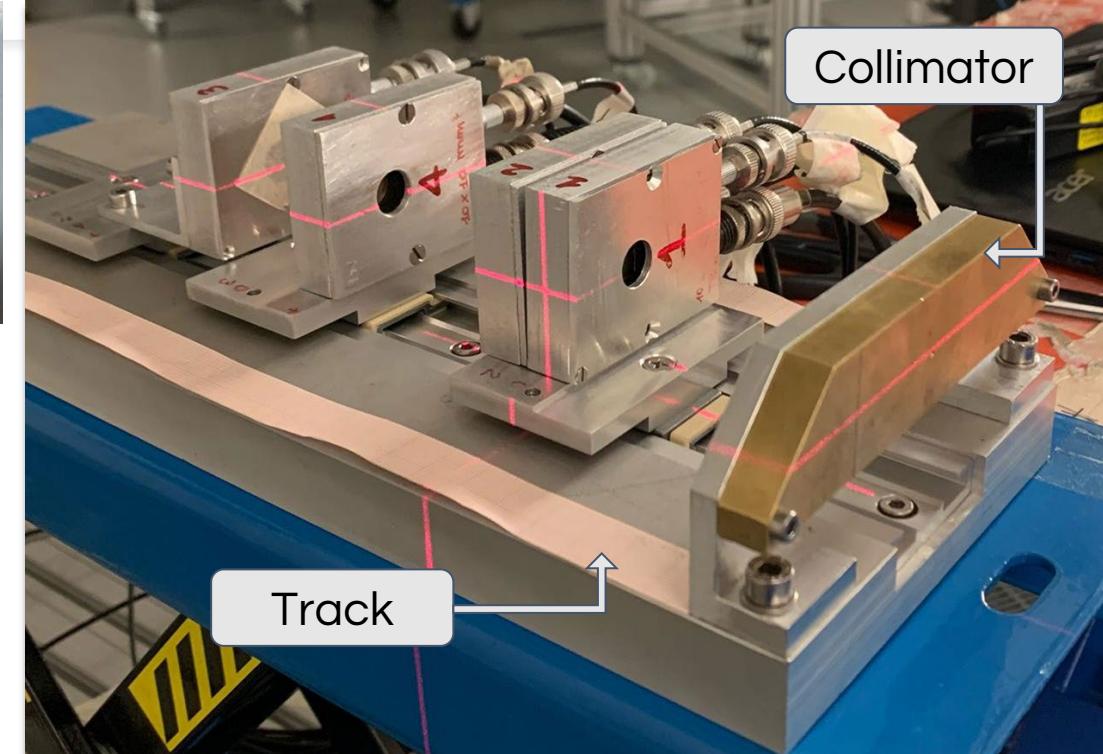
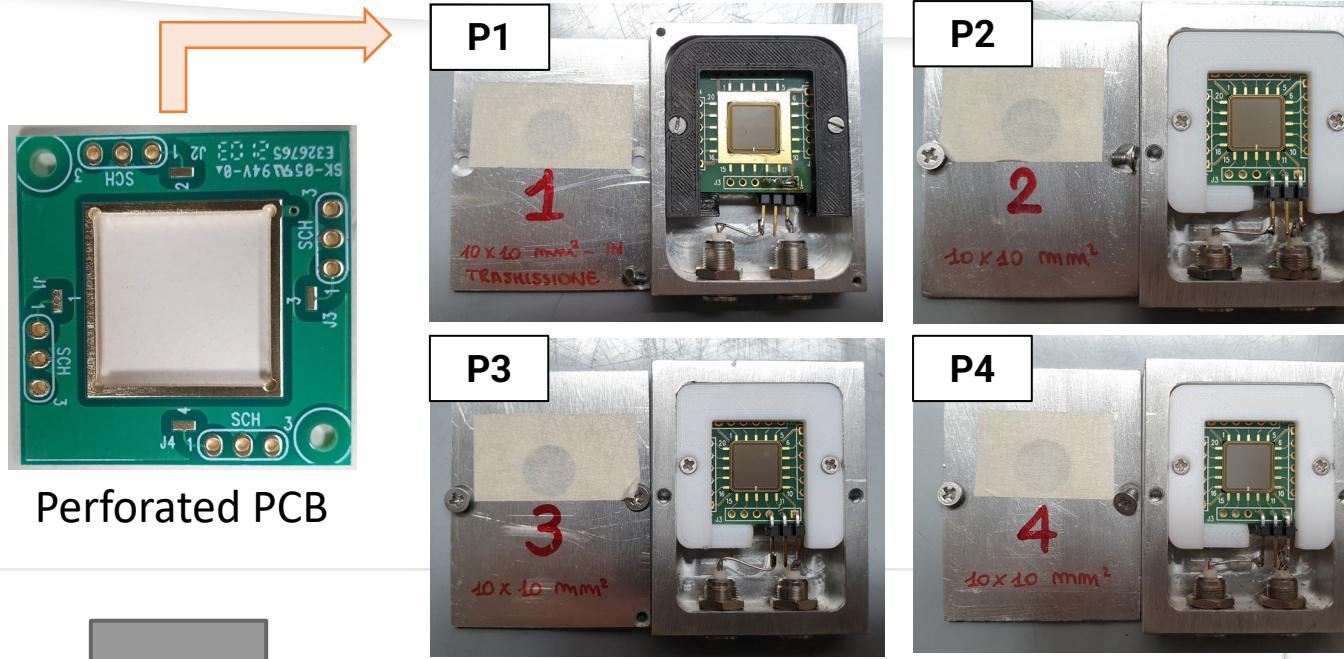
- 2 x 2 mm<sup>2</sup>
- 43,7  $\mu\text{m}$

# Detector prototype

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# PRAGUE

## The realization of a prototype made of 4 SiC detectors

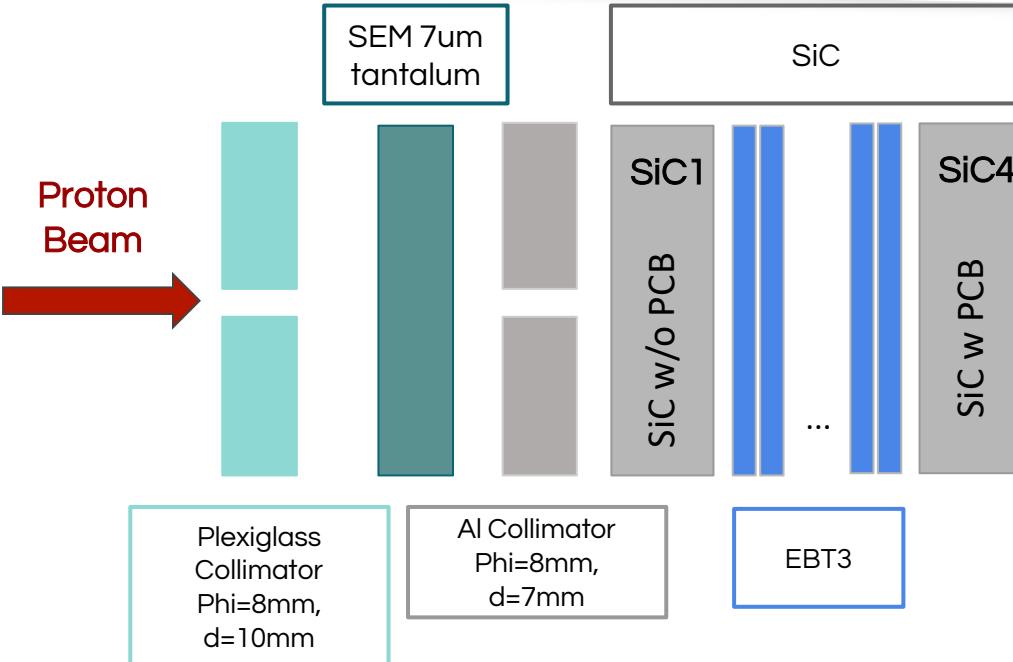


Aluminum boxes contain a 1 x 1 cm<sup>2</sup> detector

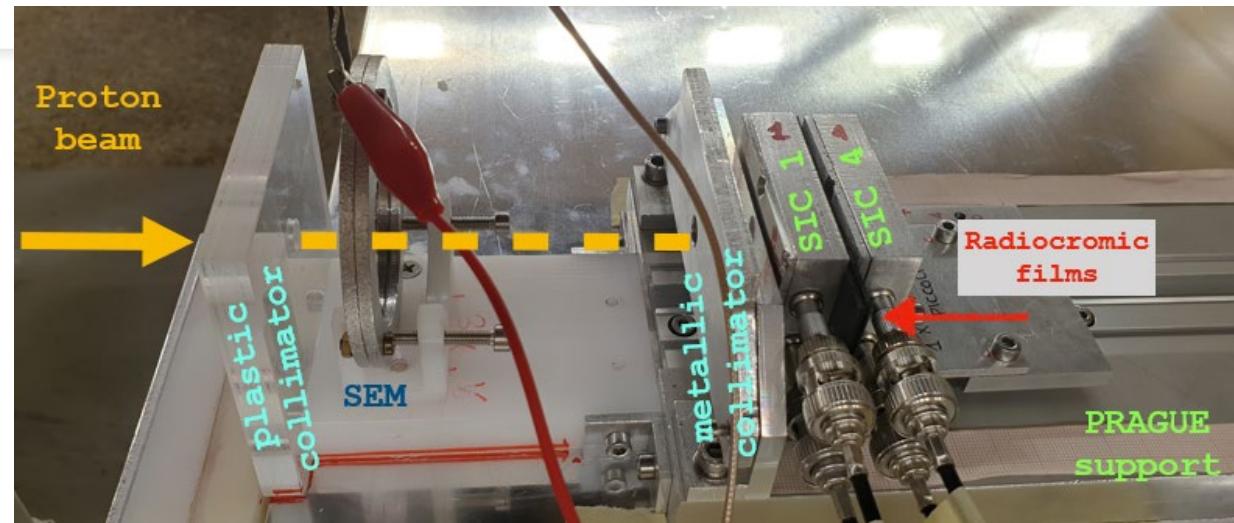
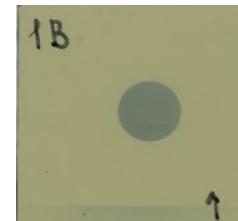
- active layer of **10,3 μm**
- passive layer of **125,67 μm**
- mounted on **PCB**.

# PRAGUE prototype - Experimental campaign @ Institute of Nuclear Physics Av Čr, Řež

## Configuration 1



- ❑ Proton **beam energy**: 35 MeV
- ❑ **Fluence**:  $10^8$  protons/cm<sup>2</sup>
- ❑ **Irradiation field**: circular shape; 10 mm in diameter
- ❑ **SEM**: Secondary Emission Monitor



Holder for EBT3 in stack configuration



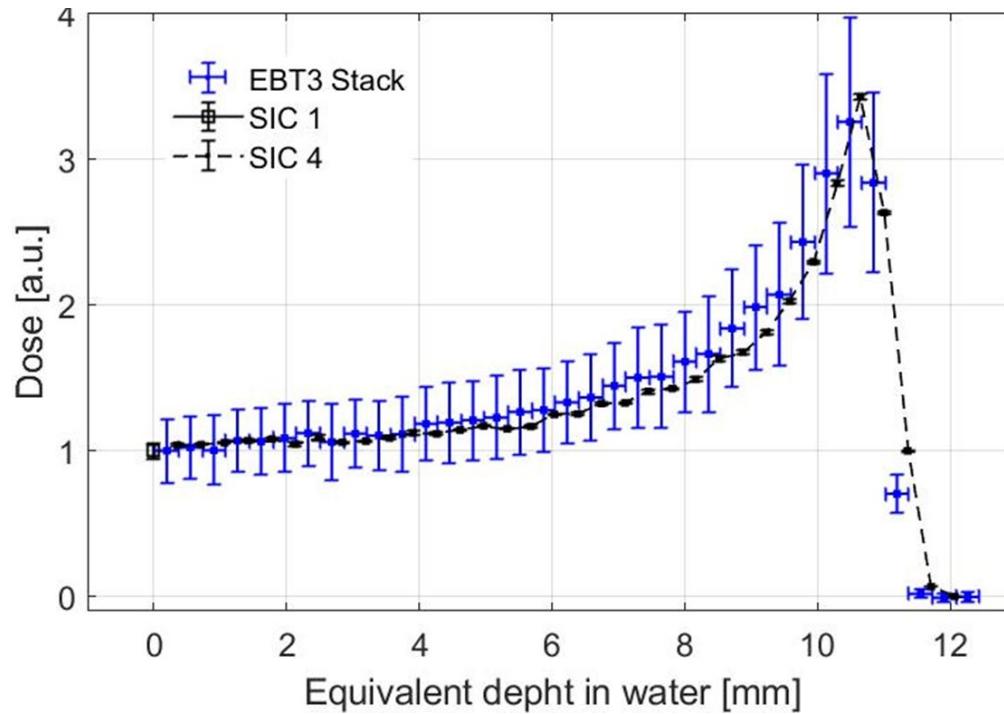
## What has been done?

- Estimation of the WET of the detectors
- Acquisition of the PDD distribution using a stack of EBT3 gafchromic films
- Acquisition of the PDD distribution by varying the number of the EBT3 absorbers between the first and second detector

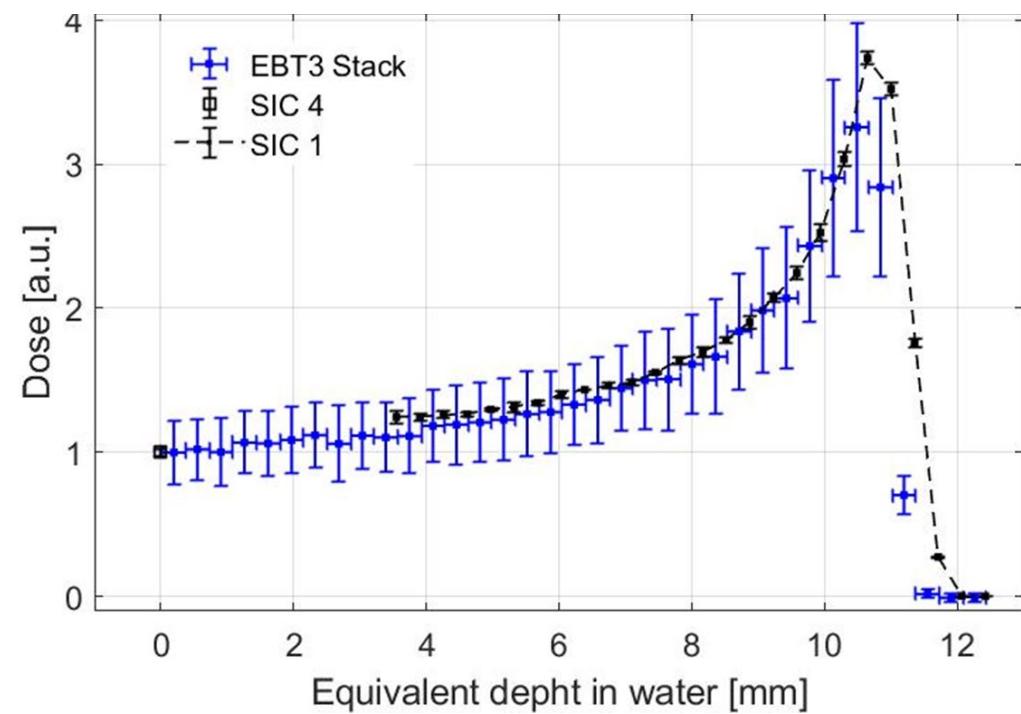
# PRAGUE prototype - Experimental campaign @Institute of Nuclear Physics Av Čr, Řež



Bragg Peak reconstruction using SiC4 detector  
 (configuration 1)



Bragg Peak reconstruction using SiC1 detector  
 (configuration 2)

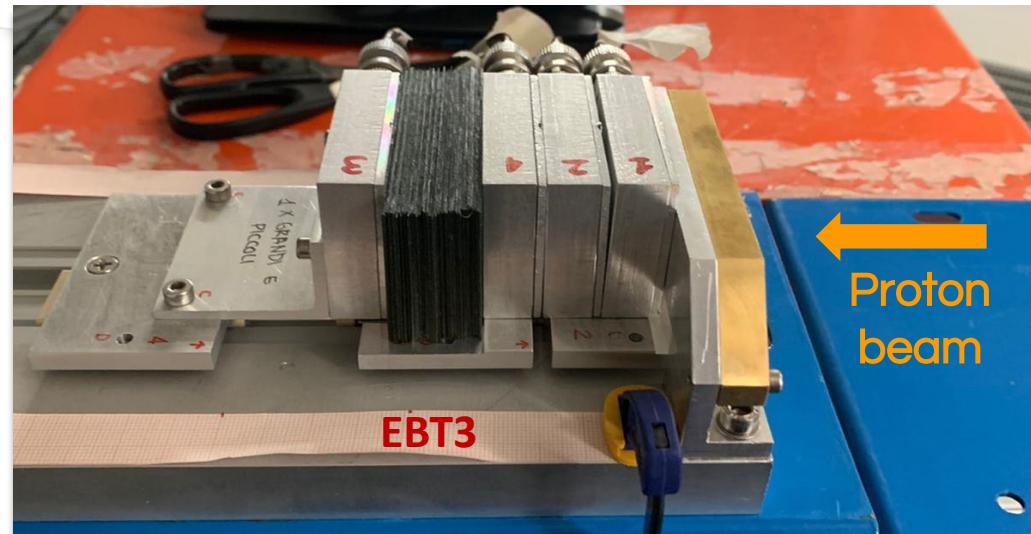


Good agreement within experimental errors!

EBT3 Peak - Plateaux ratio	SiC Peak - Plateaux ratio Conf.1	SiC Peak - Plateaux ratio Conf.2
3.25496	3.43025	3.73533

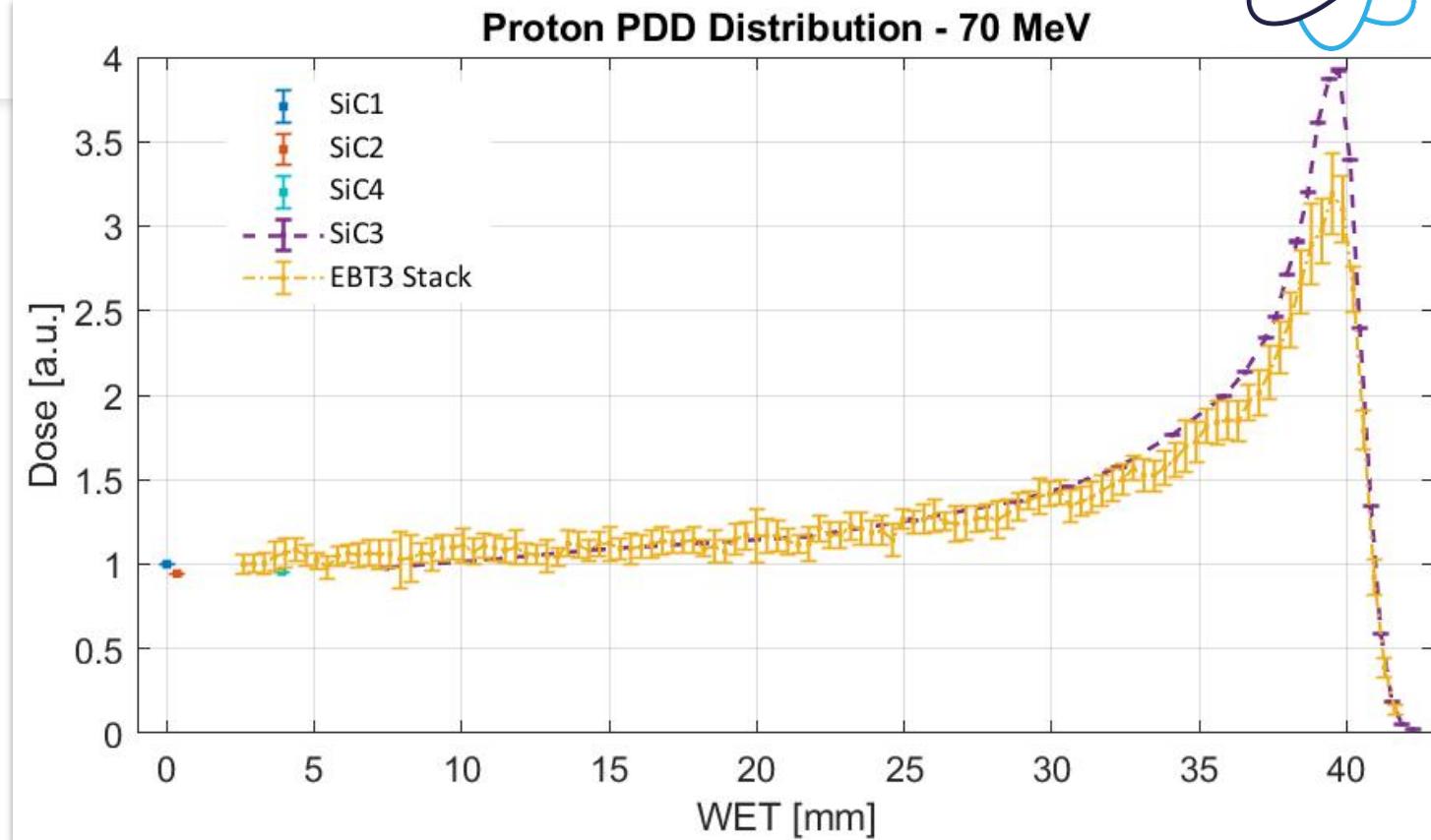


# PRAGUE prototype - Experimental campain @Trento Proton Therapy Centre



Istituto Nazionale di Fisica Nucleare

- Proton beam energy:** 70 MeV
- Intensity:**  $10^8$  protons/s
- Irradiation field:** circular shape - 10 mm in diameter
- Clinical proton beam dose-rate**
- Ionization chamber** provided by the center: it returns the number  $N$  of protons incident on the collimator. It is used to monitor the beam current.



GAF PEAK [mm]	SIC PEAK [mm]	EBT3 Peak - Plateaux ratio [a.u.]	SiC Peak - Plateaux ratio [a.u.]
$39.6 \pm 0.2$	$39.8 \pm 0.2$	3.3	3.9

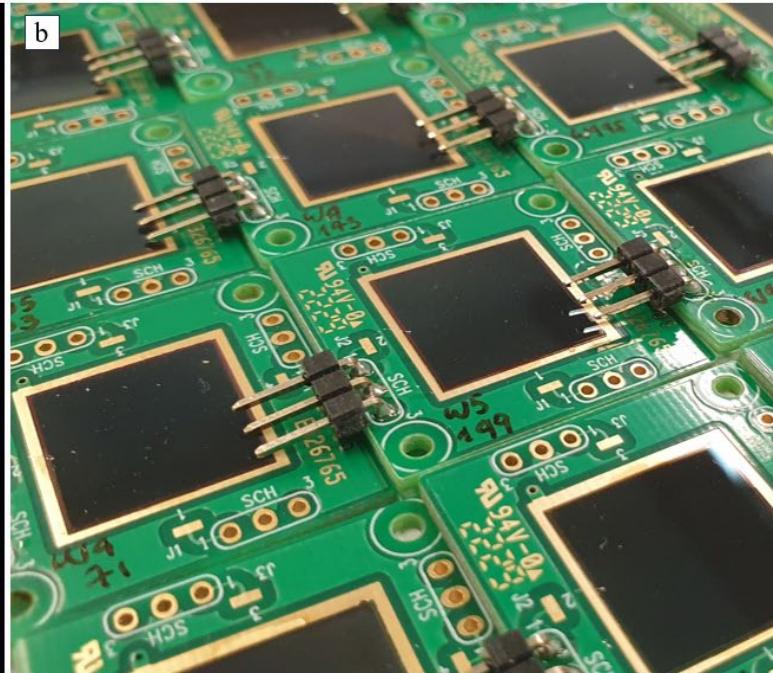
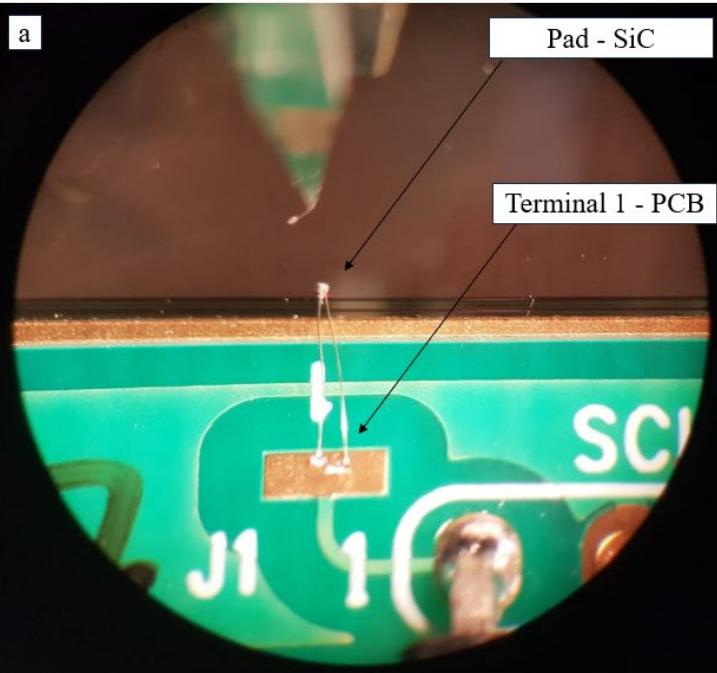
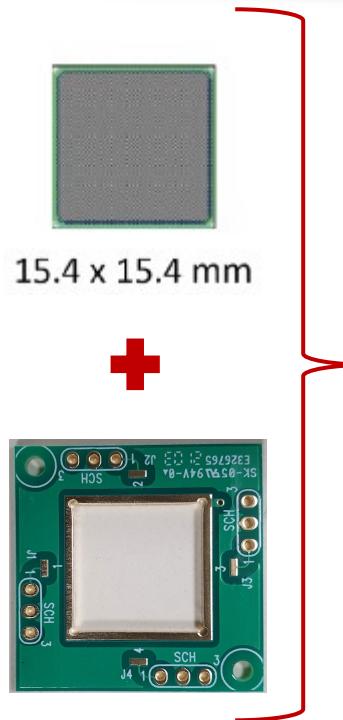
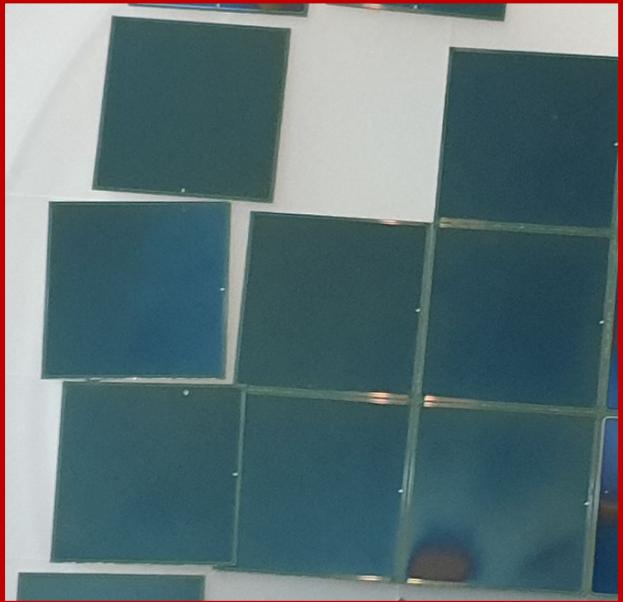
The results are consistent with the previous ones!

# Final configuration

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# Final detectors assembly

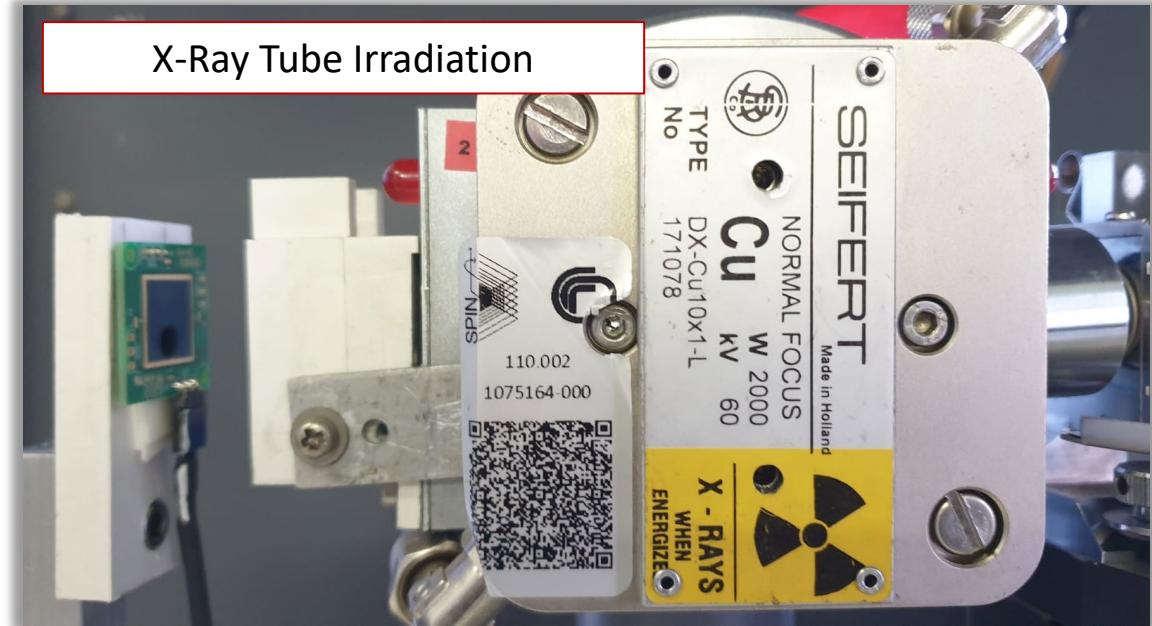
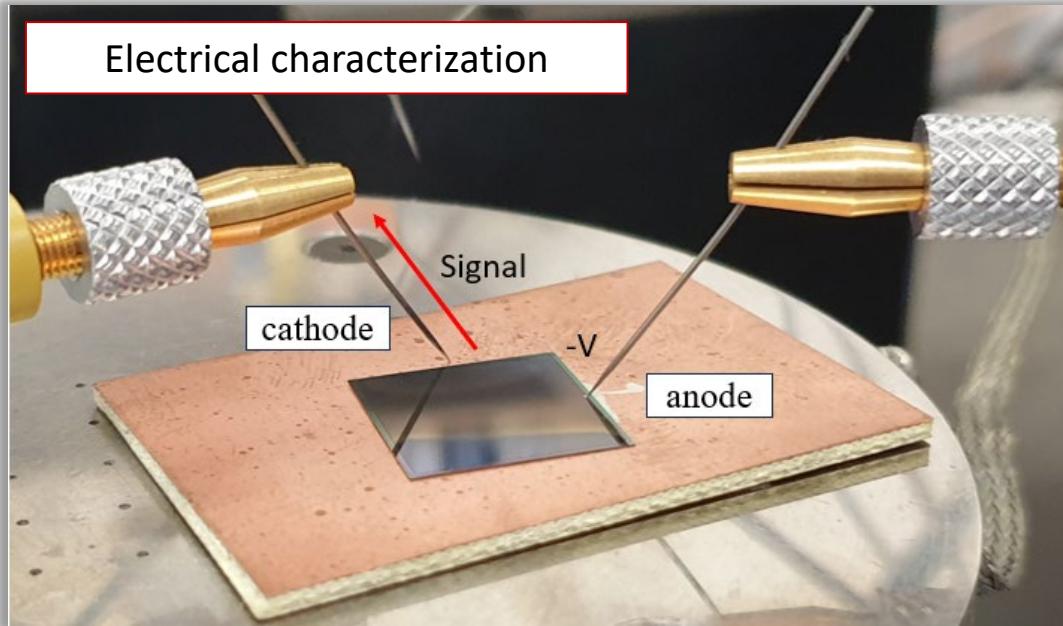
## 80 SiC devices:



1. SiC were glued to the perforated PCB with silver conductive glue
  2. A wire bonding (1-2 mils) was performed between the pad and the PCB at terminal 1
  3. Electrical pins have also been welded to the PCB board

- $p^+ \rightarrow 0,3 \mu\text{m} - N_A = 1 \cdot 10^{19} \text{ cm}^{-3}$
  - $n \rightarrow 10 \mu\text{m} - N_D = 8 \cdot 10^{13} \text{ cm}^{-3}$
  - Substrate  $\rightarrow N_D = 0,5 - 1 \cdot 10^{14} \text{ cm}^{-3}$

# Final detectors characterization



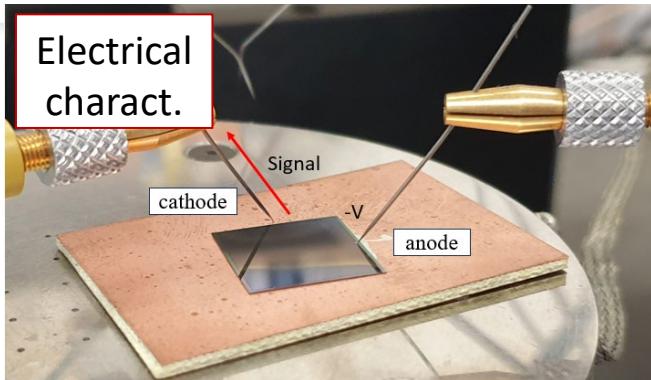
Tests:

- **IV profile** → we selected 50 “good” SiC
- **CV profile**

Tests:

- **Stability**
- **CCE**
- **Linearity**

# Final detectors: CV profile



- **Saturation capacitance** → minimum C;
- **Depletion voltage** → intersection method;
- **Depletion region thickness:**

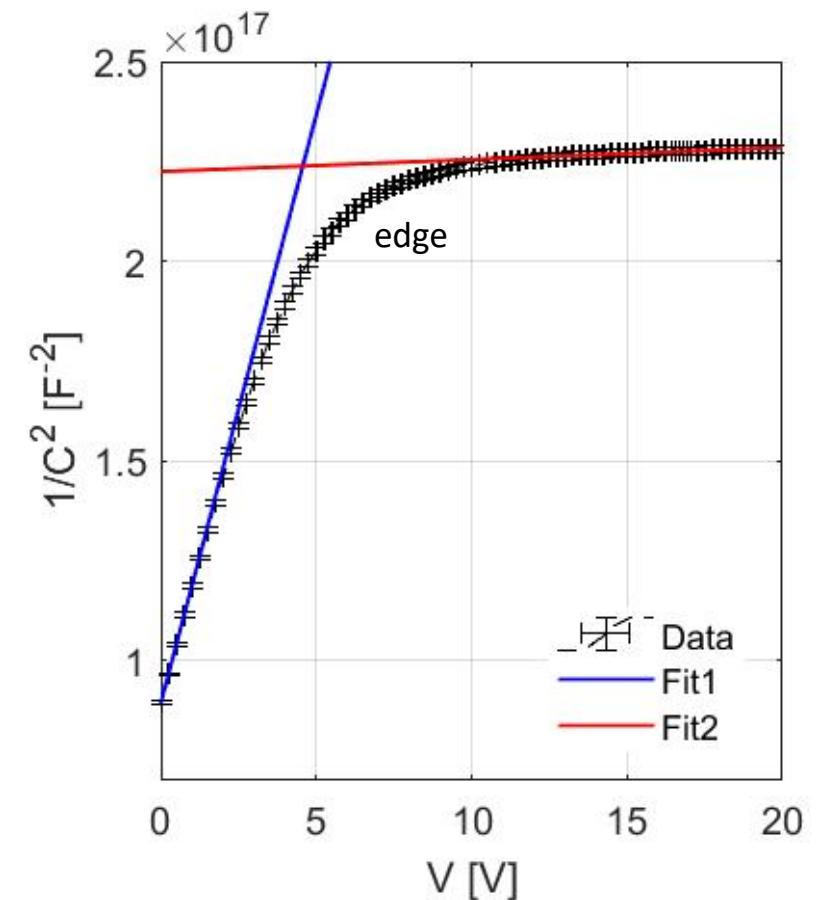
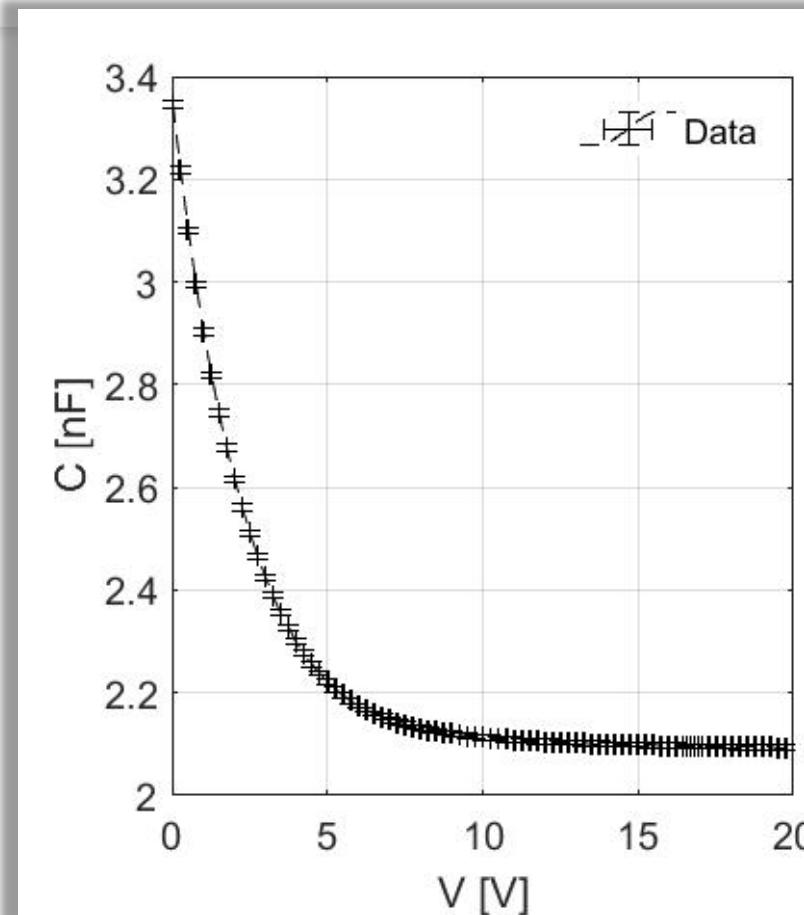
$$W = \frac{A \cdot \epsilon_s}{C_s}$$

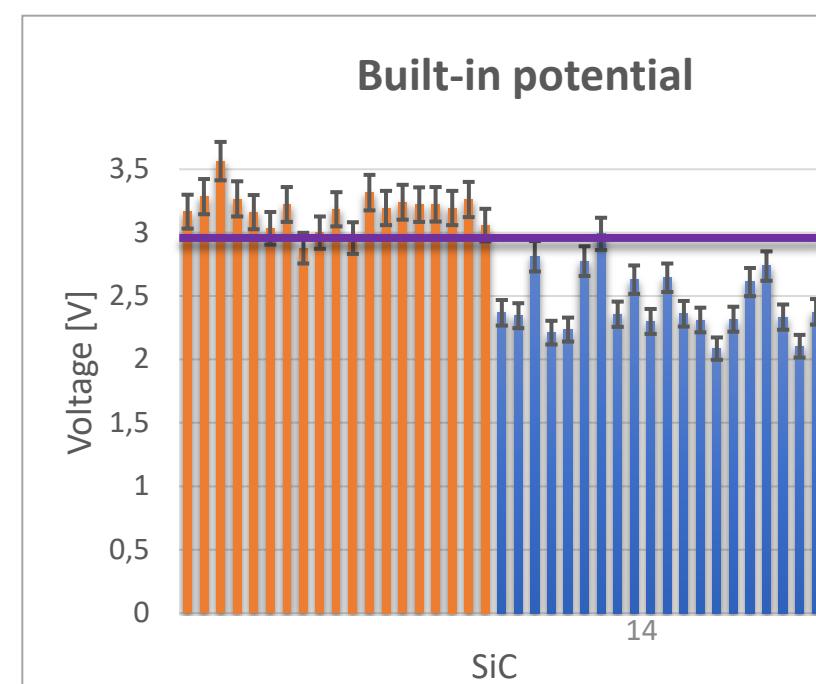
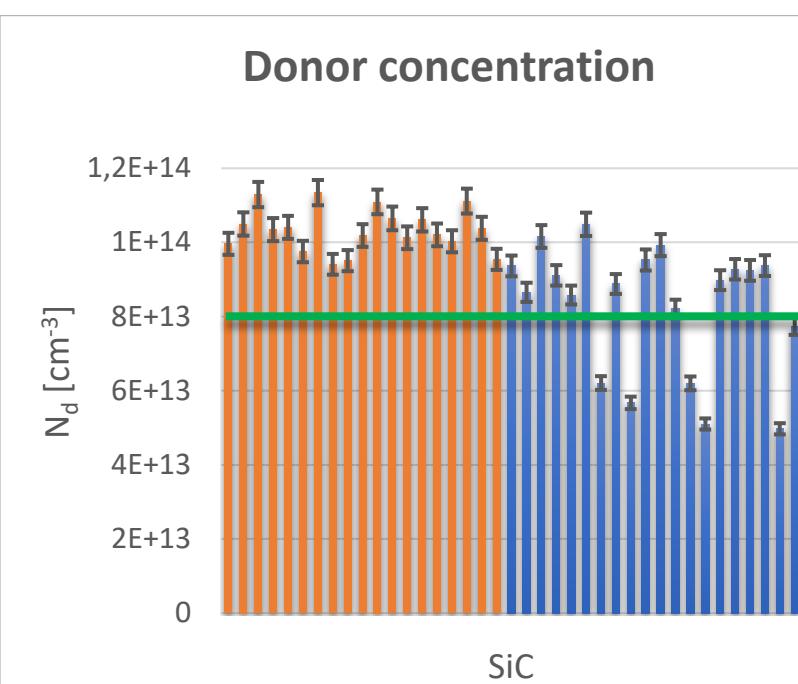
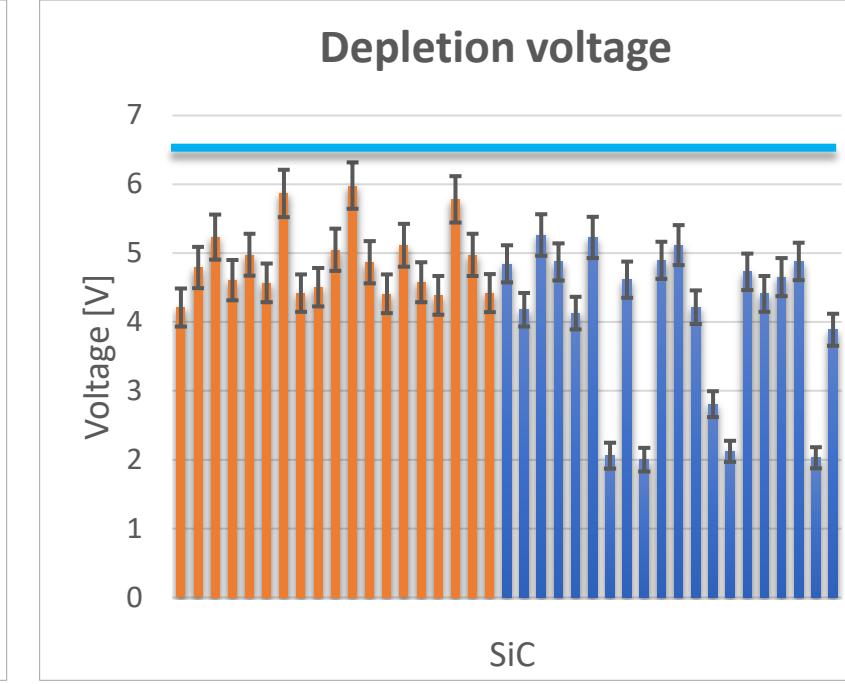
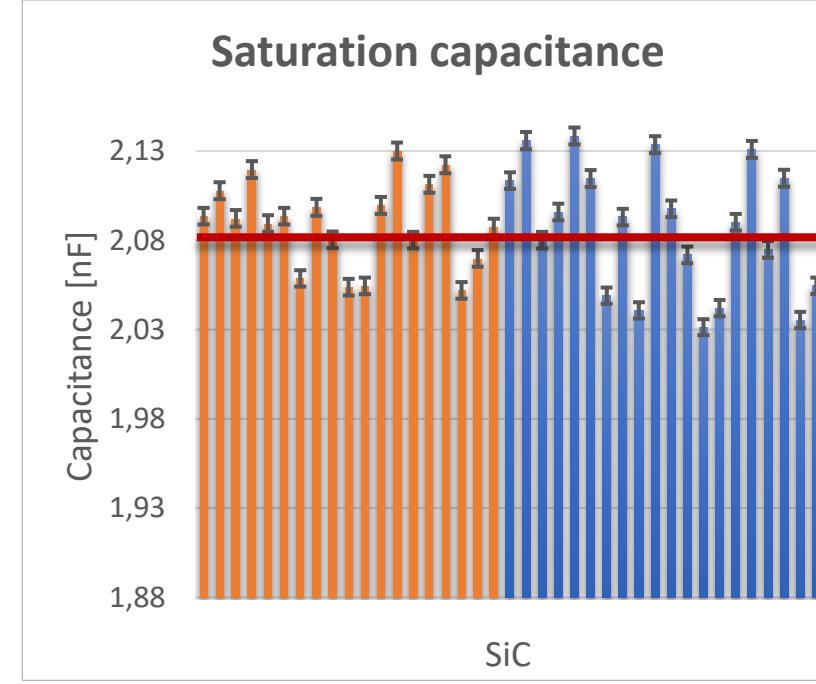
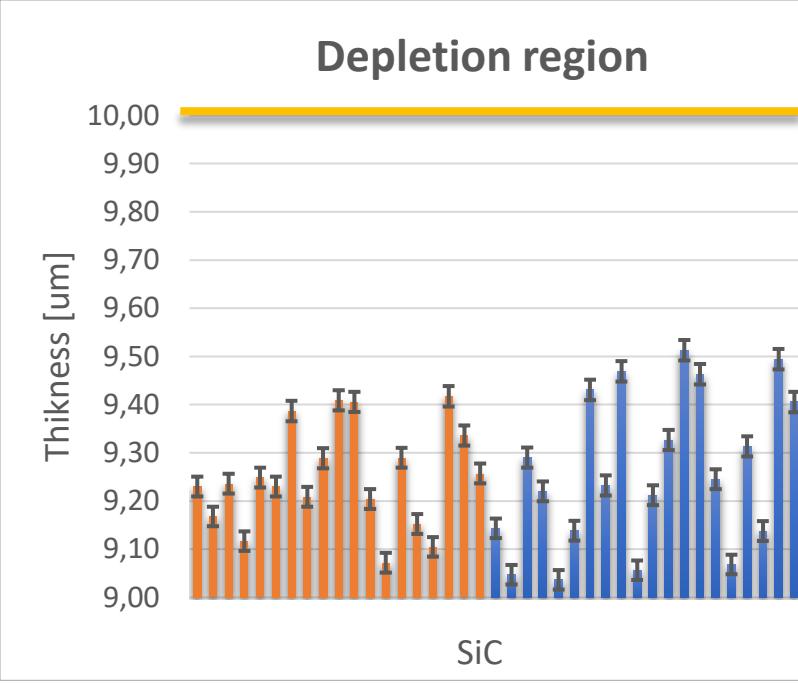
- **Built-in potential** - Fit1 parameters:

$$V_{bi} = \frac{q_1}{m_1}$$

- **Donor concentration** - Fit1 parameters:

$$N_D = \frac{2}{e \cdot \epsilon_s \cdot m_1}$$





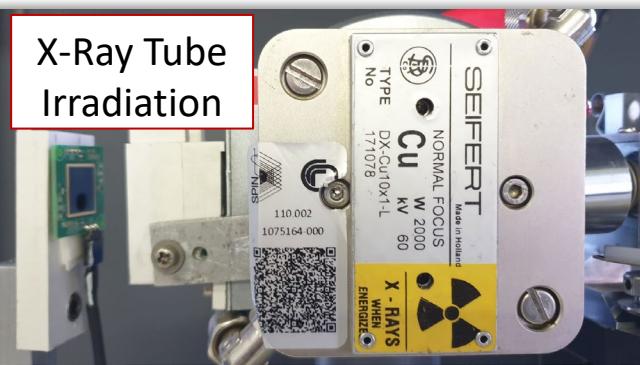
- Nominal  $W$
- $C_s = \frac{A \cdot \varepsilon_s}{W_{exp}} = 2,08 \text{nF}$
- $V_v = N_D \frac{e \cdot W^2}{\varepsilon_s} = 6,5 \text{ V}$
- Nominal  $N_d$
- $V_{bi} = 2,58 \cdot 10^{-2} \log \left( \frac{N_A N_D}{n_i^2} \right) V = 2,95 \text{ V}$

The assumptions used in the derivation of the capacitance include:

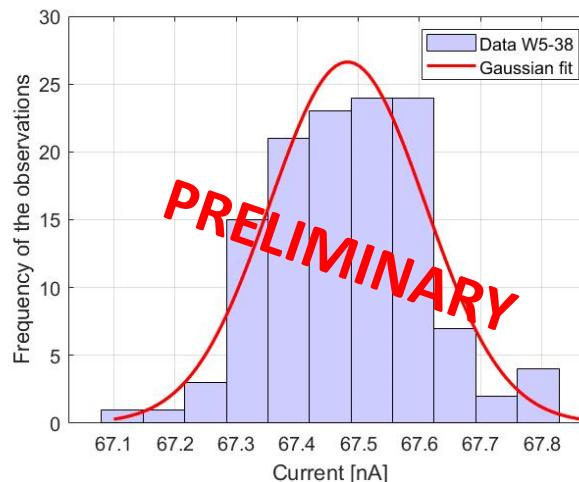
- **uniform doping;**
- abrupt junction approximation;
- planar junction.

# Final detectors: Stability & CCE

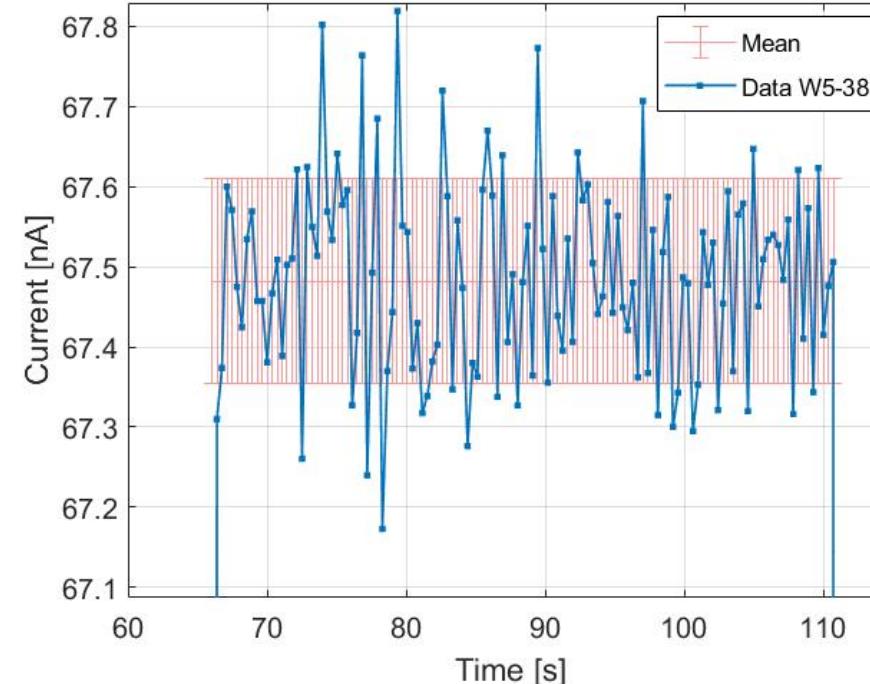
X-Ray Tube  
Irradiation



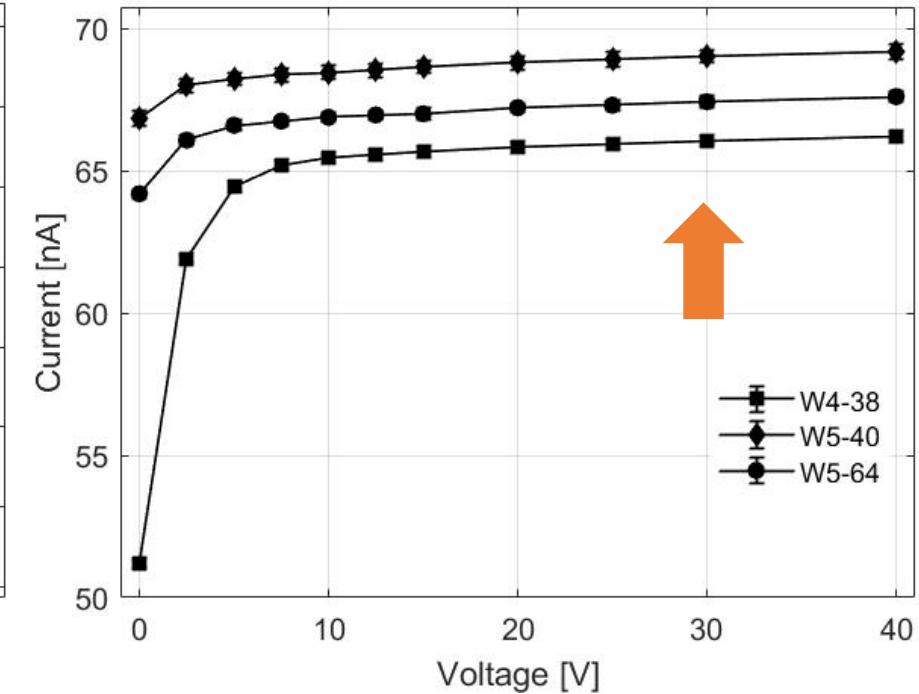
Voltage Tube: 10 kV  
Current Tube: 5 mA



$\chi^2$  test  
Random fluctuations!



63.8% of fluctuations within  
0.5% of the mean value.

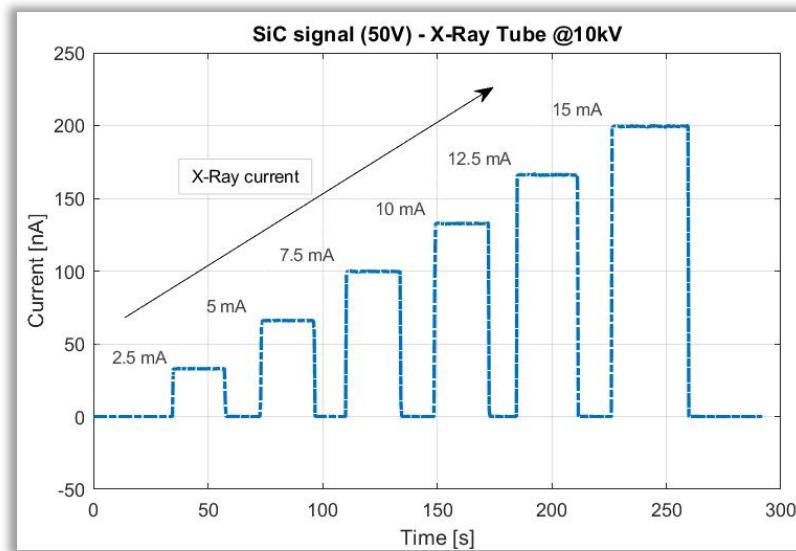
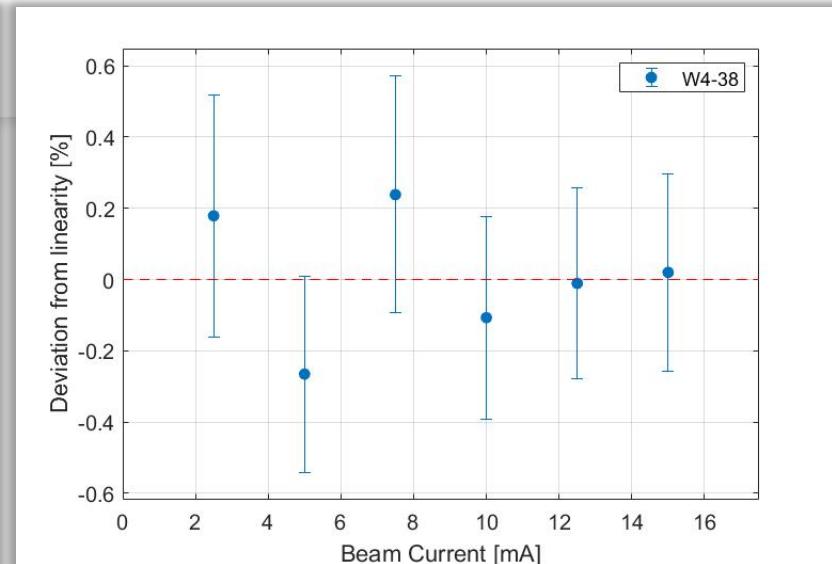
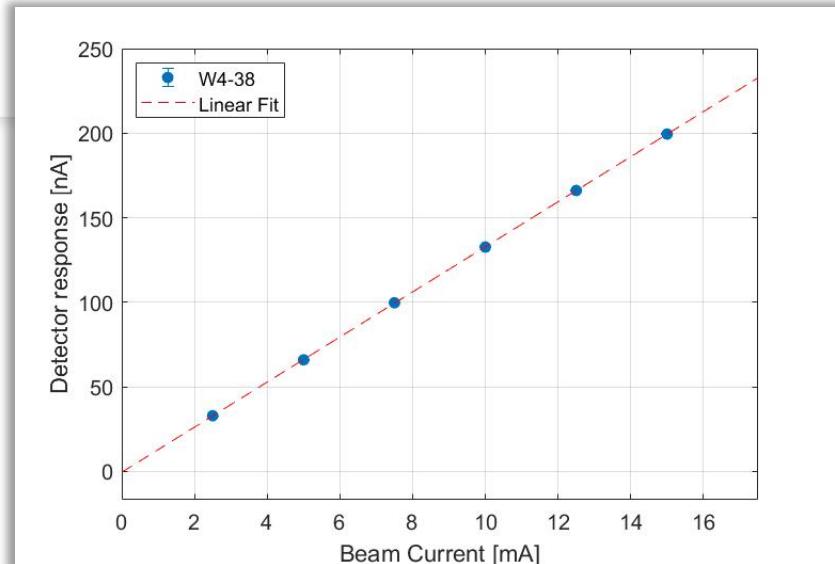


Saturation region @30 V.

# Final detectors: linearity

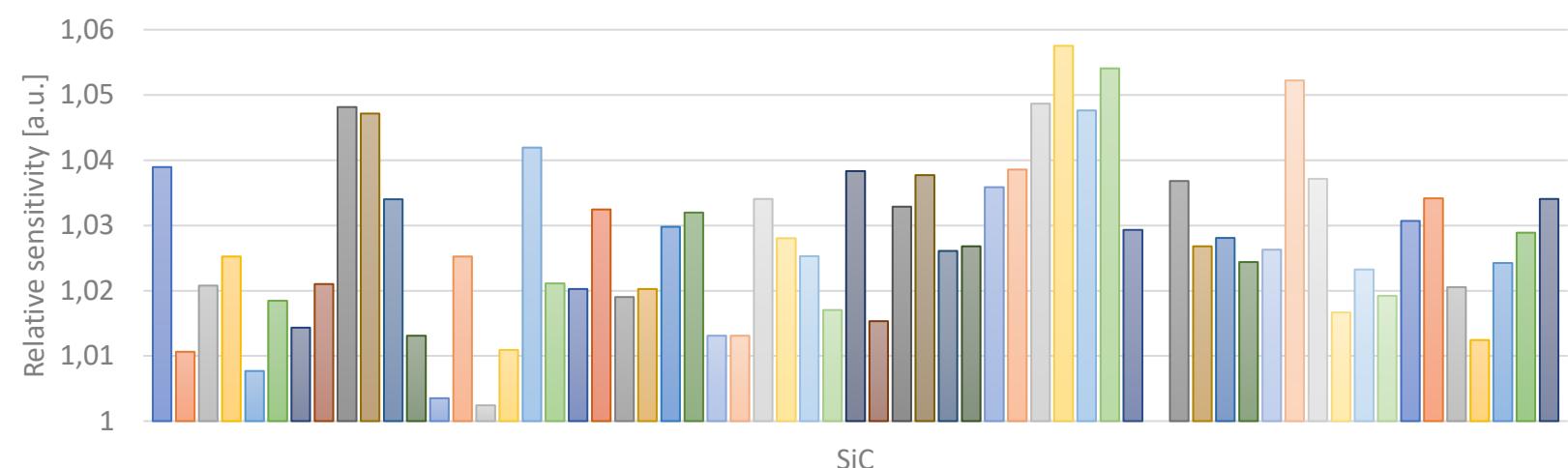


Voltage Tube: 10 kV  
 Current Tube: 2.5 - 15 mA



The slopes represent the sensitivity of the detectors.

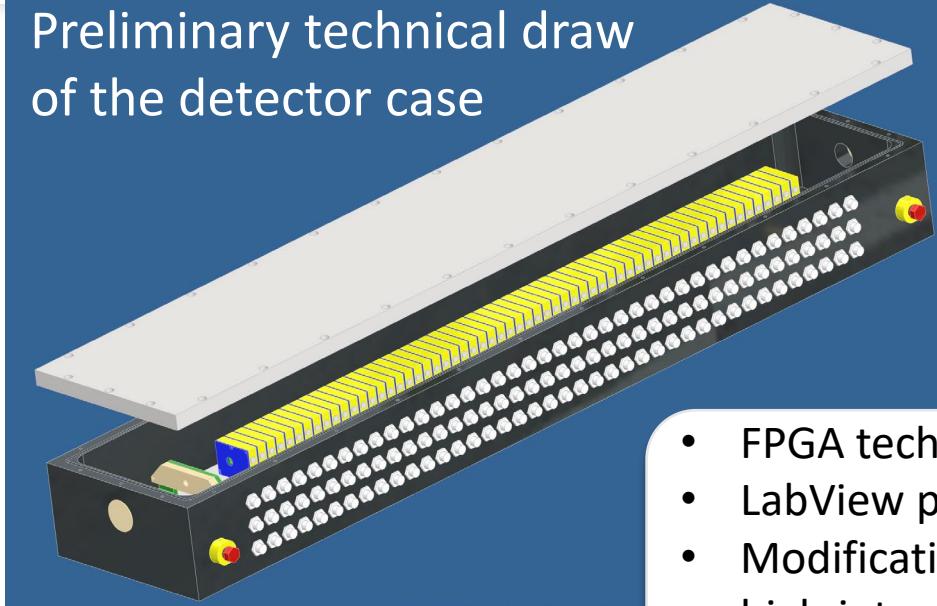
Maximum deviation: 1,5%. in 90% of cases < 1%



# Electronic chain & detector case

**DETECTOR**  
 DEVICES AND TECHNOLOGIES TORINO

Preliminary technical draw  
 of the detector case

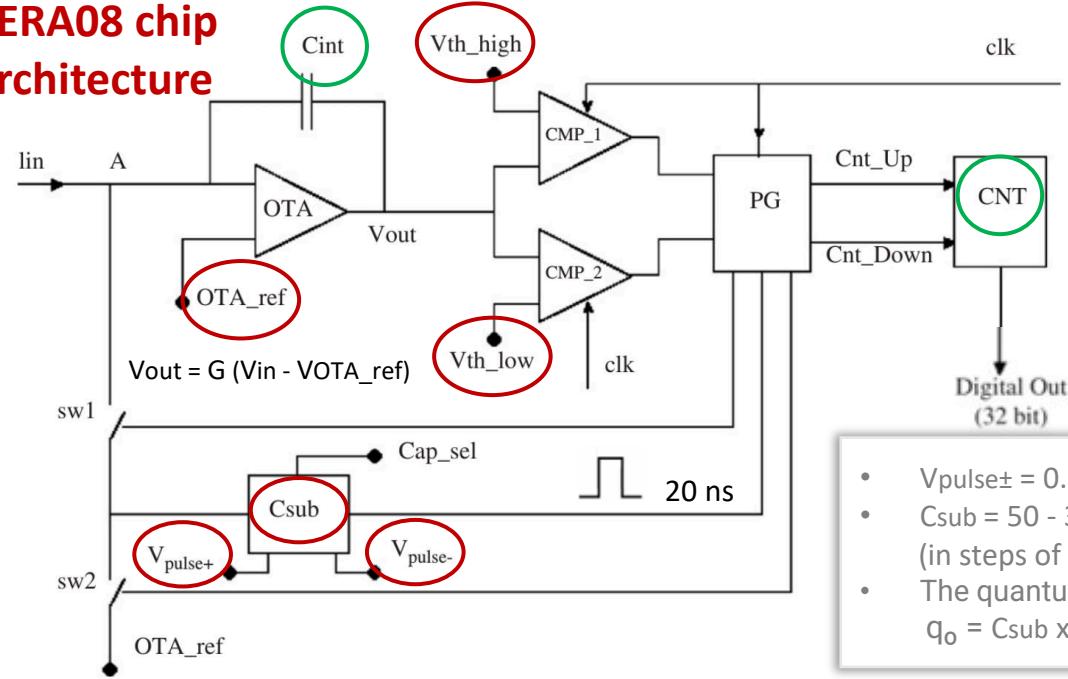


PRAGUE will provide positive signals

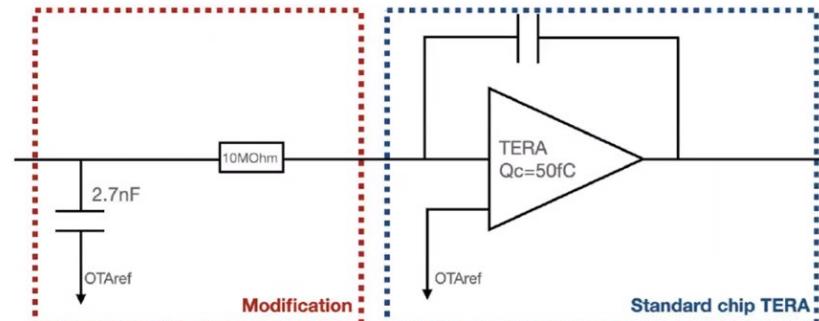
- FPGA technology
- LabView program
- Modification for high intensity beams (INFN-LNS)

- Charge-to-count/current-to-frequency converter (based on the recycling integration principle)
- 64 independent channels
- Maximum conversion frequency  $v_{max} = 20 \text{ MHz}$
- Quantum charge set  $q_o = 25 \text{ fC} - 1.155 \text{ pC}$
- Maximum input current  $I_{max} = q_o \times v_{max} = \pm 22 \mu\text{A}$

## TERA08 chip architecture



- $V_{pulse\pm} = 0.5 - 3.3 \text{ V}$
- $C_{sub} = 50 - 350 \text{ fF}$  (in steps of 50 fF)
- The quantum charge  $q_o = C_{sub} \times \Delta V_{pulse}$



# Conclusion

## Electrical characterization

- IV [0-200V/0-4V] → **50 "good" SiC devices  
20-50 pA @10-50V revers bias**
- CV [0-20V] → **Mean W: 9,25 um  
Saturation capacitance: 2nF  
Depletion voltage: 4V  
Built-in potential: 2-3 V**

## X-Ray Tube Irradiation

- Stability → **Maximum oscillation found: 0.4%**
- Linearity → **Maximum deviation from linearity:  
1,5%**
- CCE → **≈ 100% @ 30V**

## Next steps

- **Detectors**
  - Spectroscopic measurements - **in progress**
  - Proton beam irradiation – **scheduled**
- **Electrical readout**
  - realization of the new interface board - **in progress**
  - software acquisition - **in progress**
  - New board characterization– **scheduled**
- **Case detector**
  - design of the detector case - **in progress**
  - realization of the detector case - **scheduled**



# Thanks for the attention

This work was supported by the National Institute for Nuclear Physics (INFN) that funded the PRAGUE (Proton Range Measure using Silicon Carbide) project. It was also supported by European Structural and Investment Fund and the Czech Ministry of Education, Youth and Sports (Project International mobility MSCA-IF IV FZU-CZ.02.2.69/0.0/0.0/20-079/0017754).



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# Backup slides

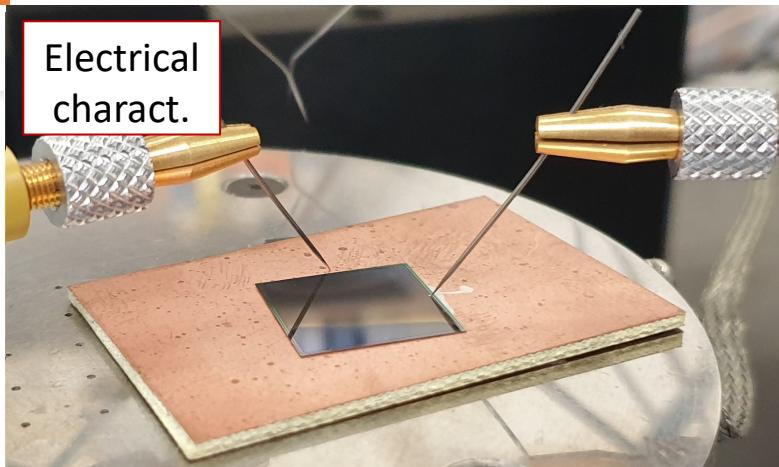
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# PRAGUE – final detectors

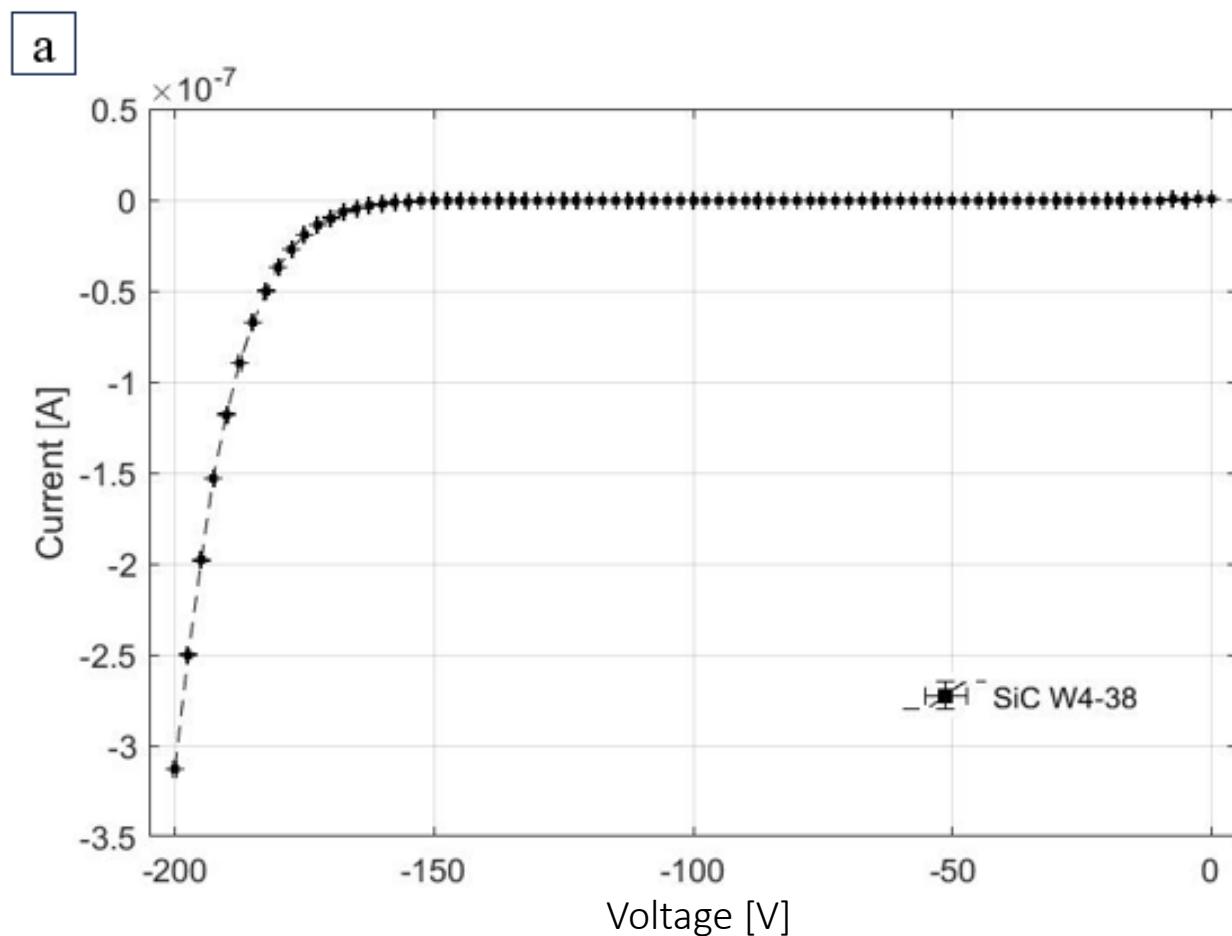
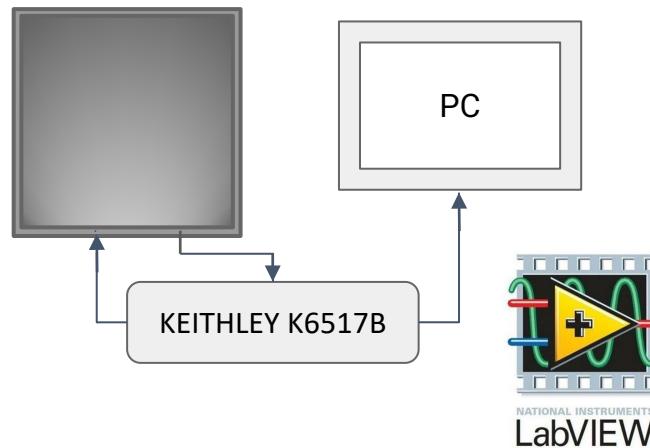


Electrical  
charact.

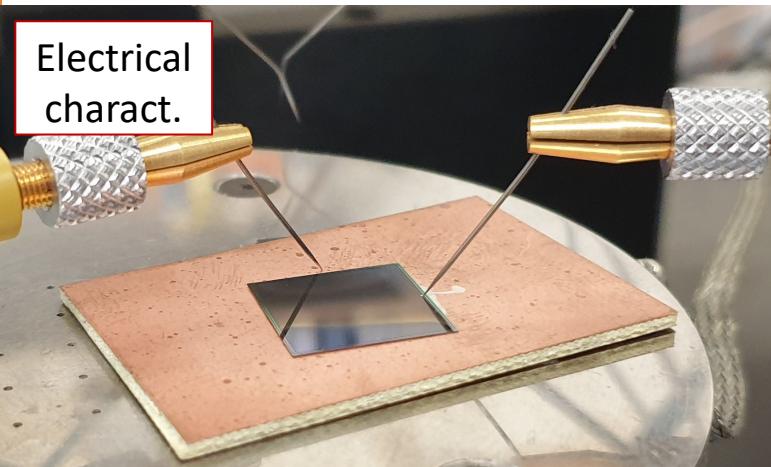


Tests:

- IV

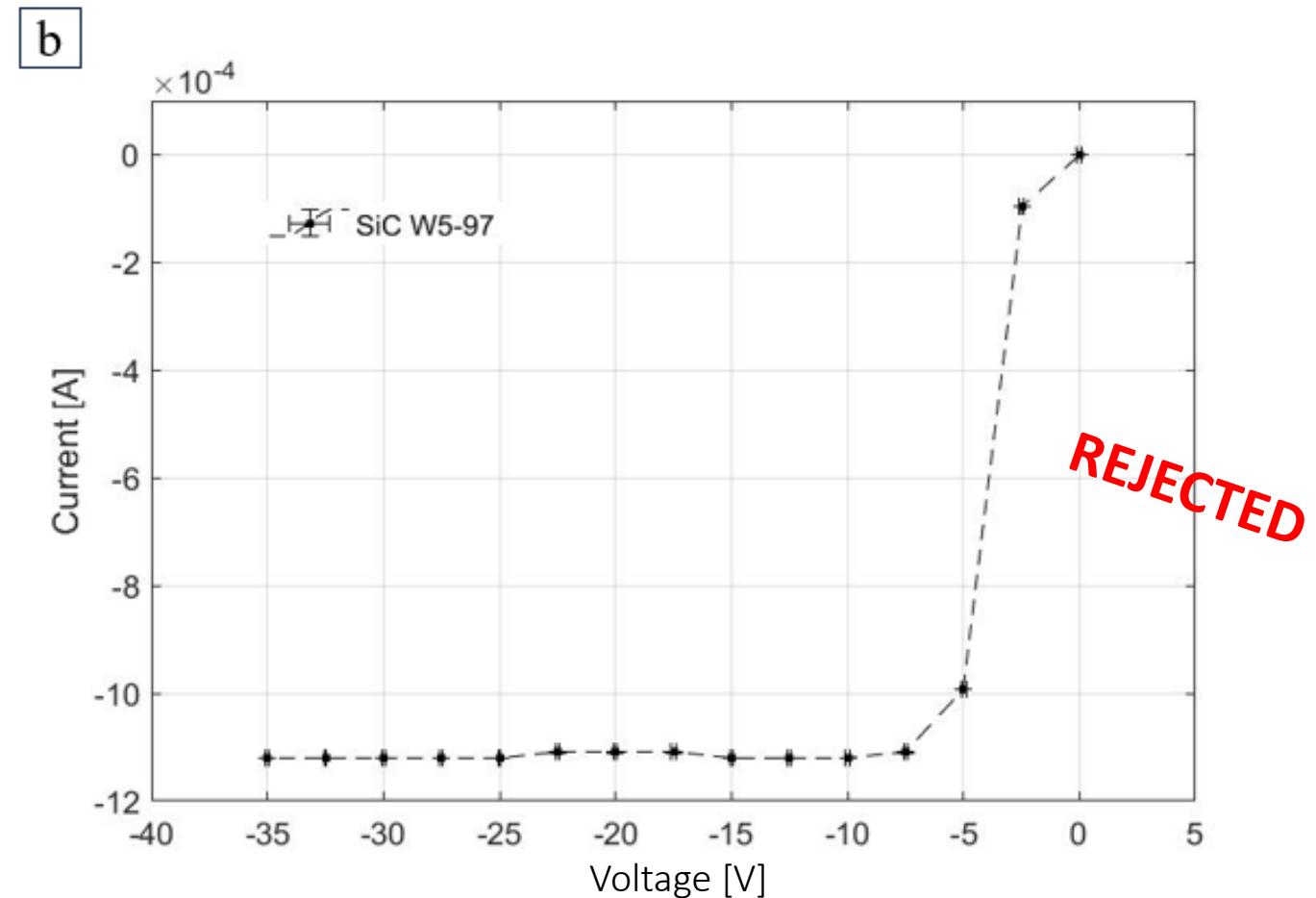
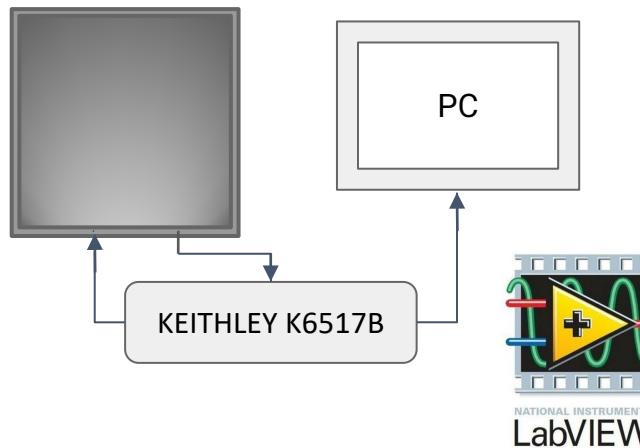


# PRAGUE – final detectors

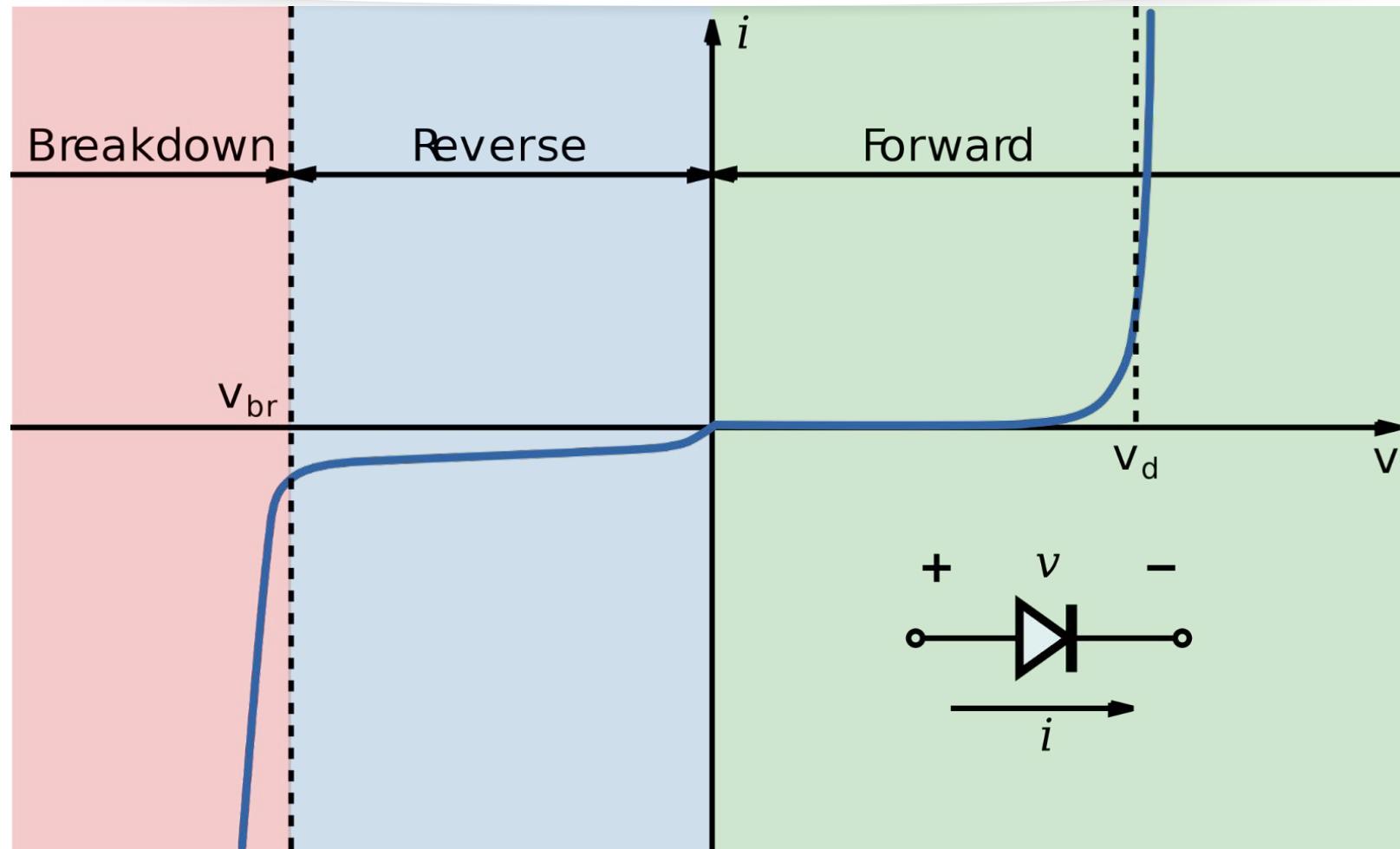


## Tests:

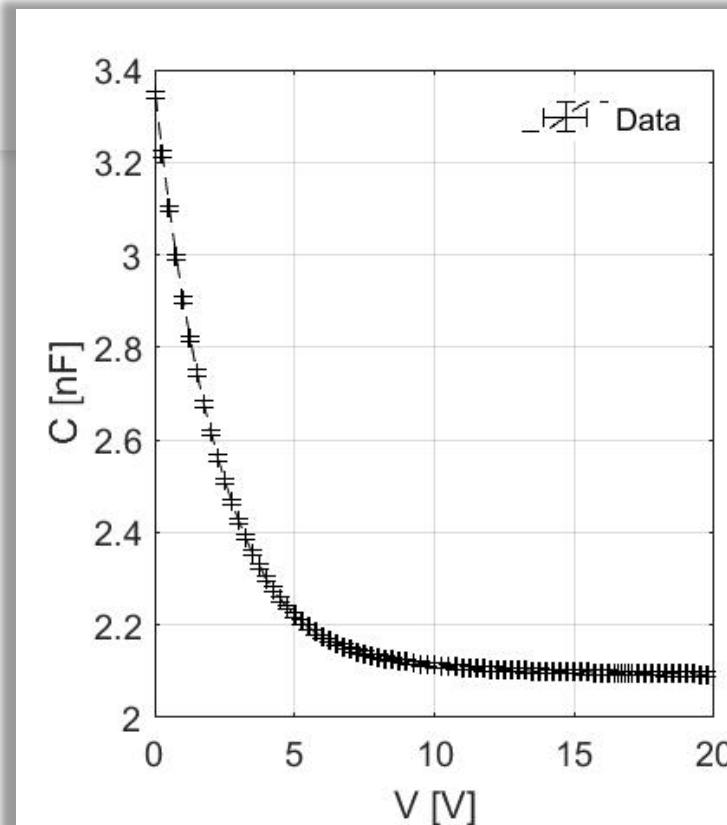
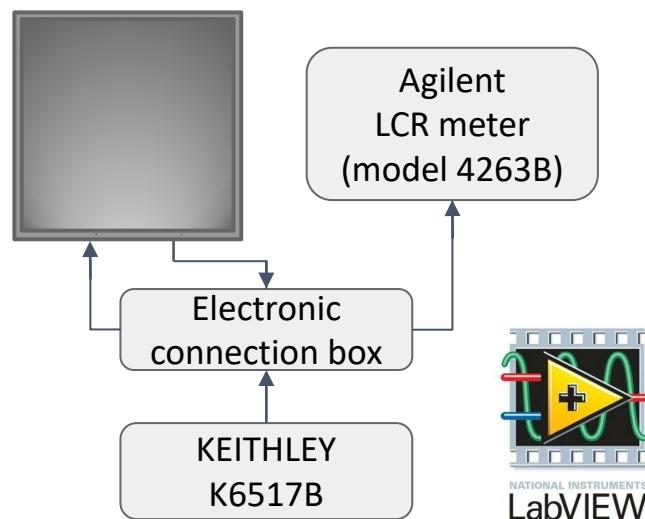
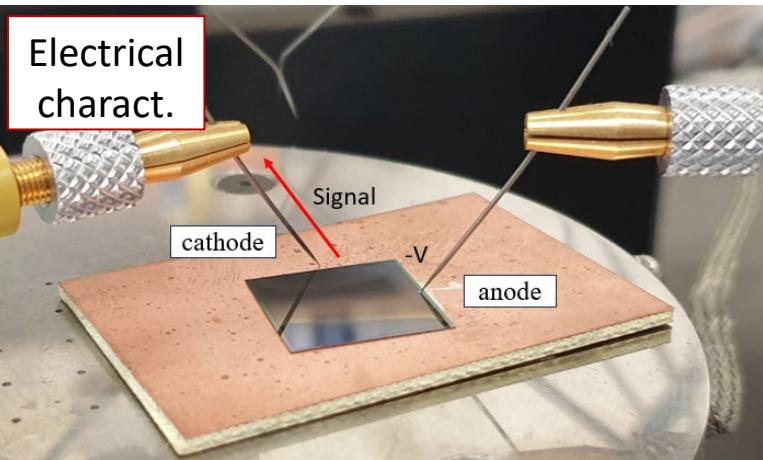
- IV → we selected 50 “good” SiC



# IV profile

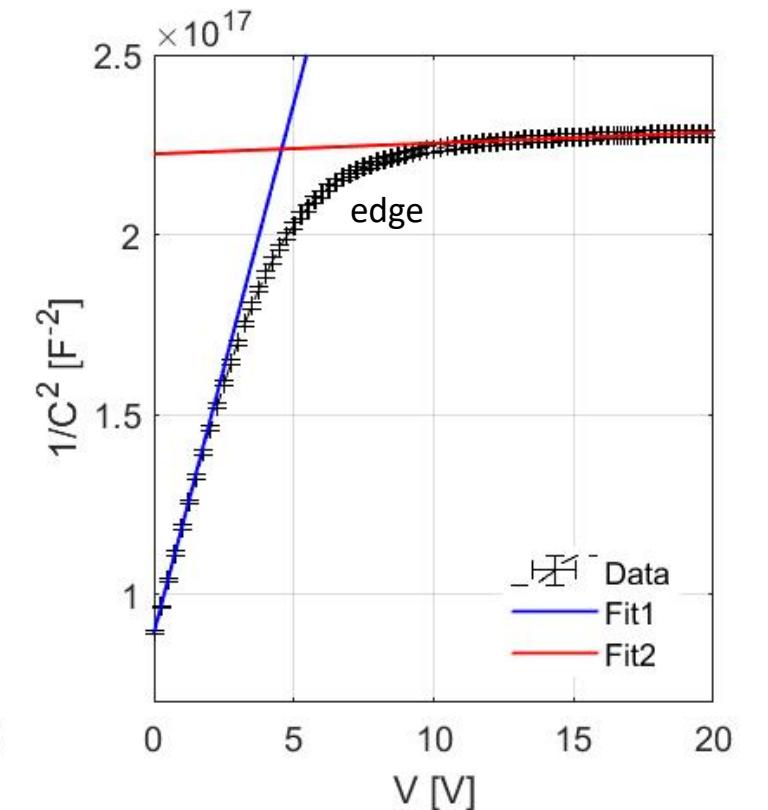


# Final detectors: CV profile



- **Saturation capacitance** → minimum C;
- **Depletion voltage** → intersection method;
- **Depletion region thickness:**

$$W = \frac{A \cdot \varepsilon_s}{C_s}$$

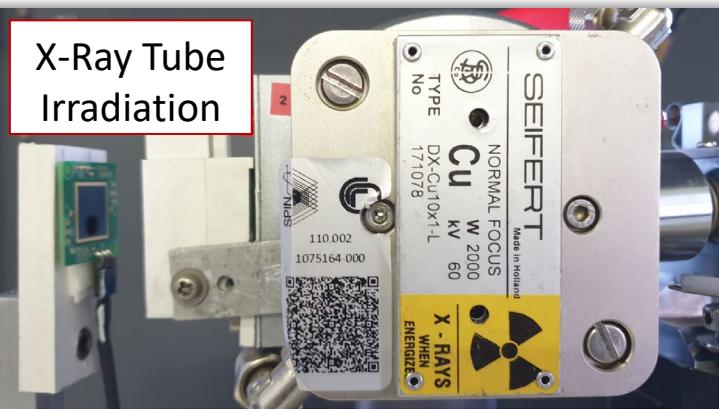


- **Built-in potential** - Fit1 parameters:  

$$V_{bi} = \frac{q_1}{m_1}$$
- **Donor concentration** - Fit1 parameters:  

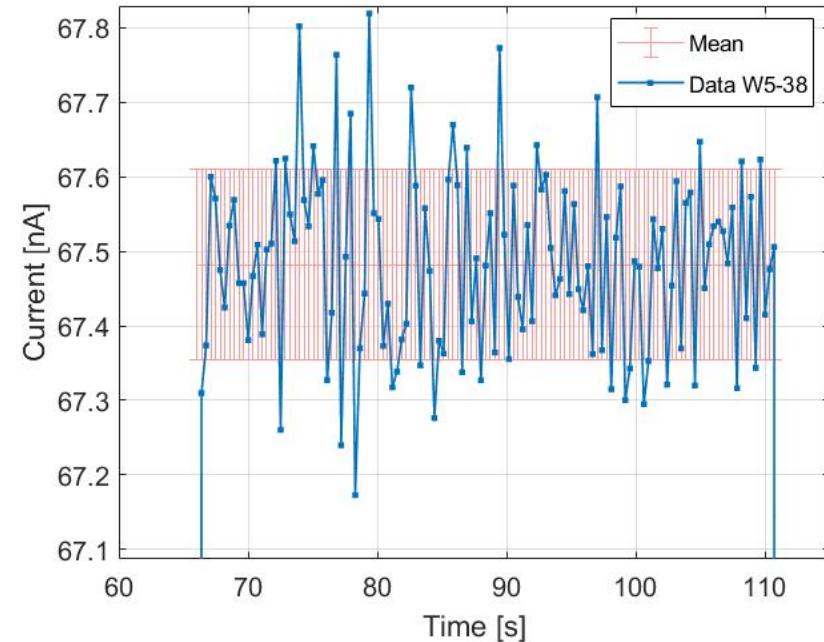
$$N_D = \frac{2}{e \cdot \varepsilon_s \cdot m_1}$$

# PRAGUE – final detectors

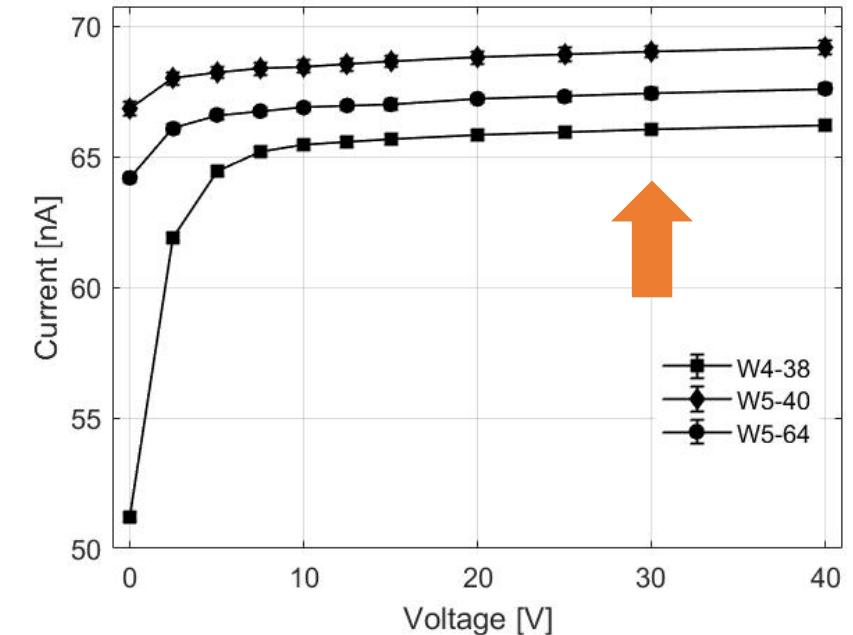
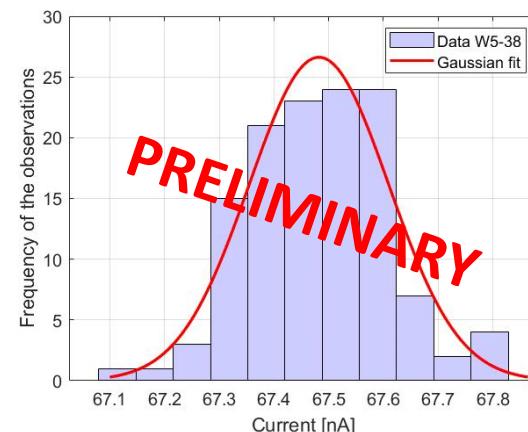
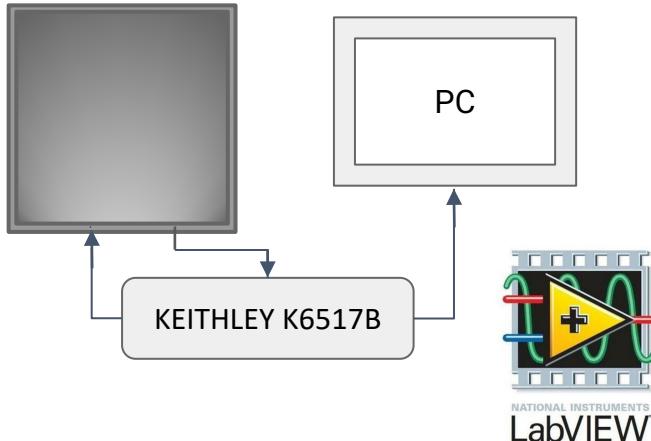


Tests:

- Stability
- CCE



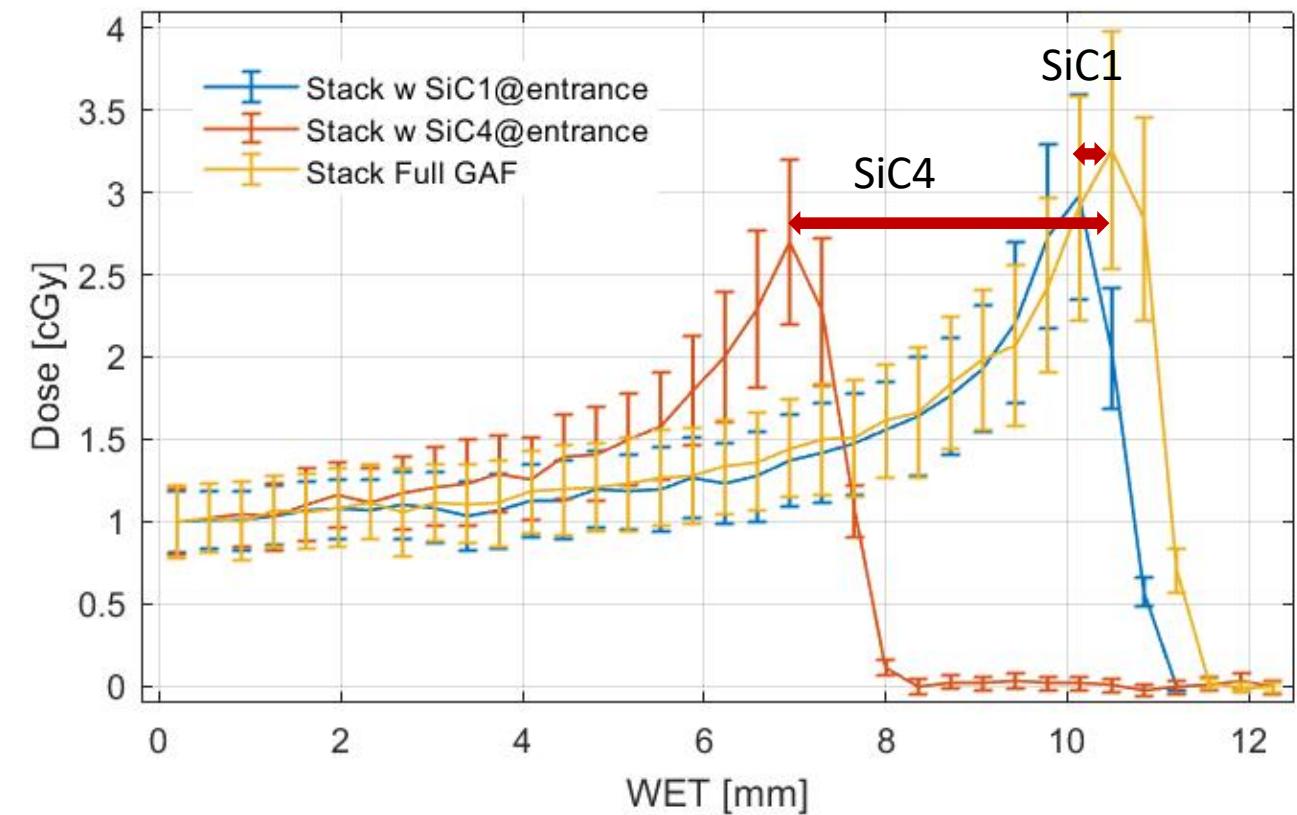
Sampling rate: 3Hz  
 Full scale: 200 nA  
 Reverse voltage: 30V  
 Voltage Tube: 10 kV  
 Current Tube: 5 mA



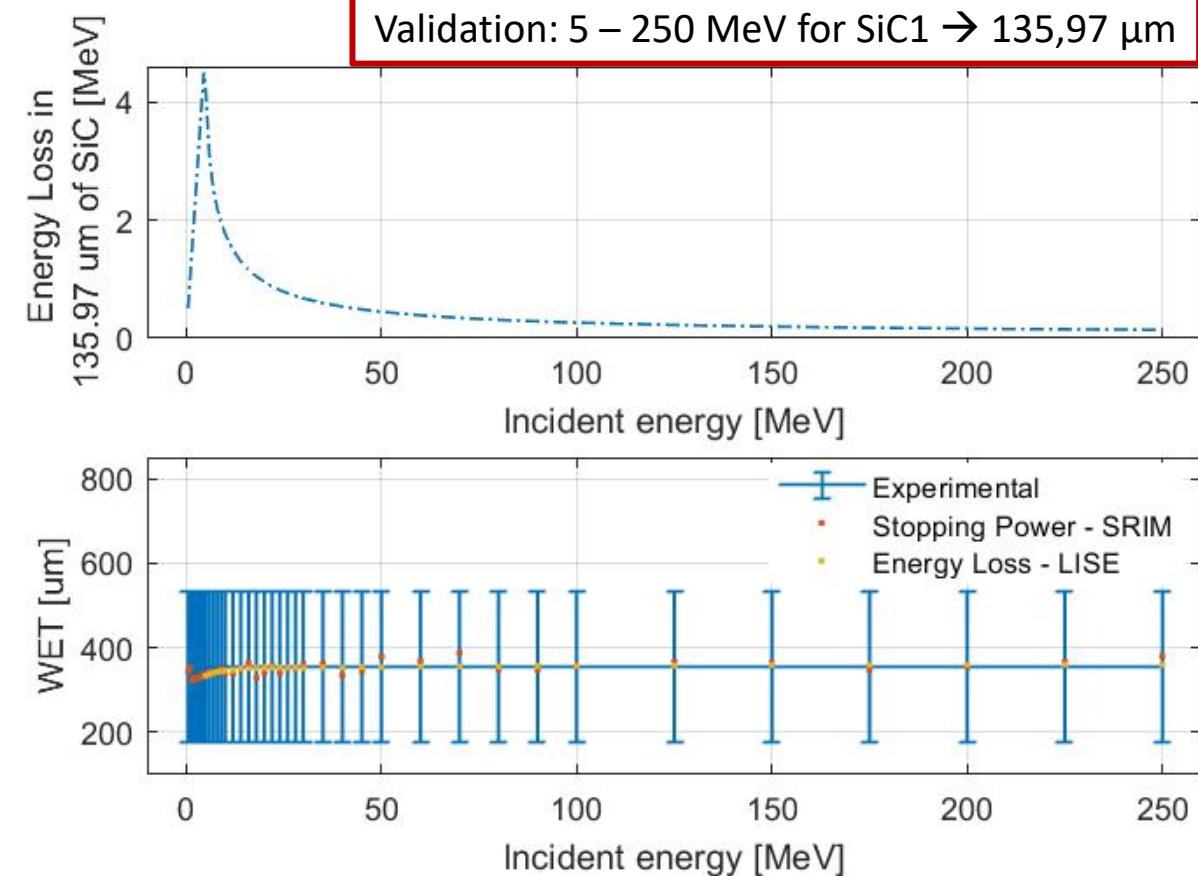
63.8% of fluctuations within  
 0.5% of the mean value.

$\chi^2$  test:  
 Random fluctuations!

# PRAGUE prototype - Experimental campaign @ Institute of Nuclear Physics Av Čr, Řež



**SiC1 = 0,355±0,177 mm → 1 EBT3 EQUIVALENT**  
**SiC4 = 3,55±0,177 mm → 10 EBT3 EQUIVALENT**



$$t_w = t_m \frac{\rho_m}{\rho_w} \frac{S_m(E_i)}{S_w(E_i)}$$

Thin-target approach  
**Stopping power ratio (SPR) approximation**

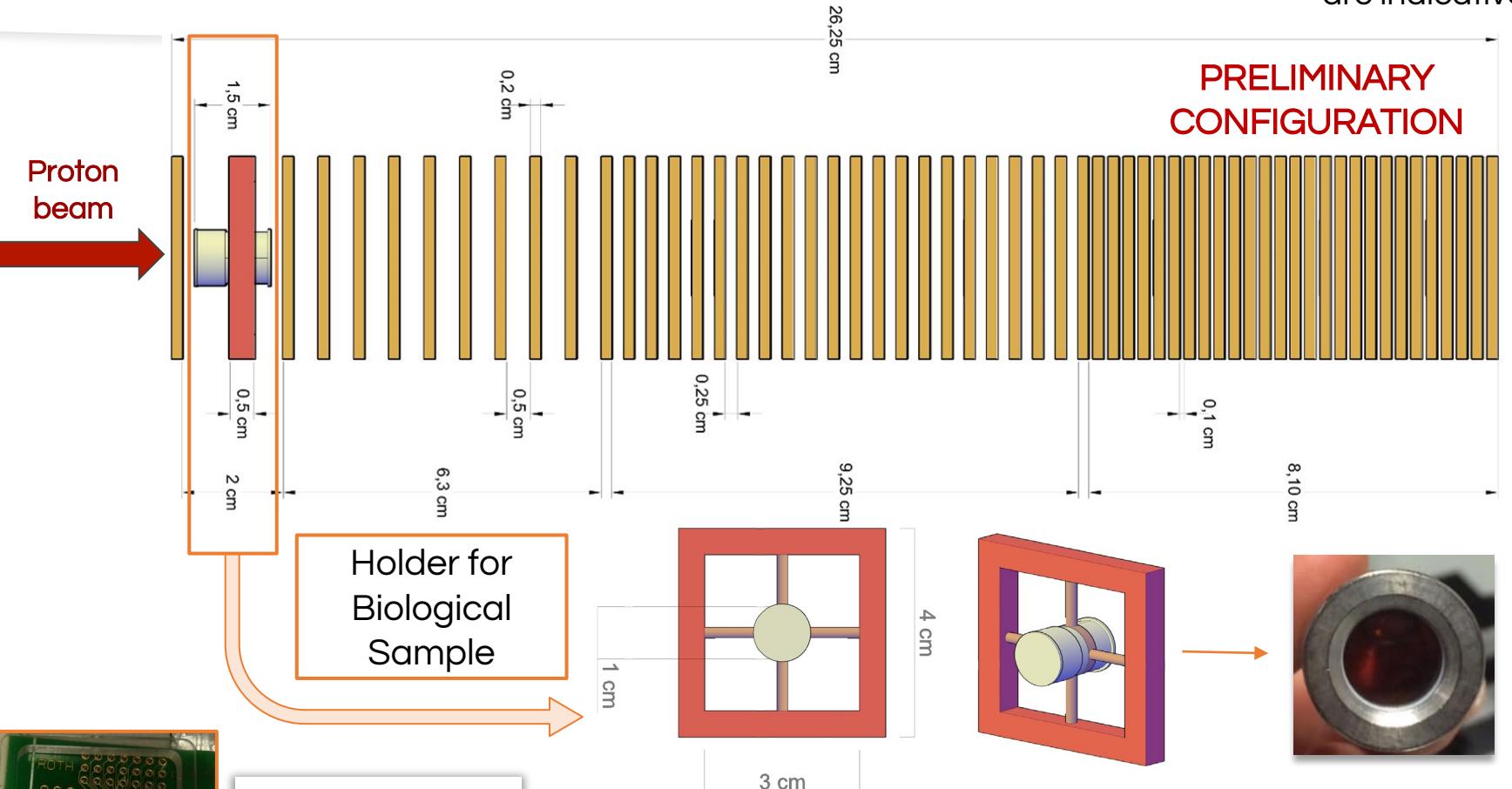
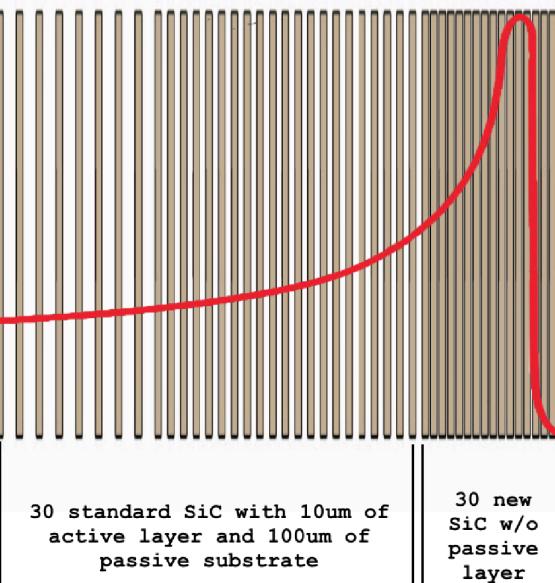
# PRAGUE

## (Proton RAnGe measure Using silicon carbidE) detector

2  
7

Main goal!

First dosimeter able to reconstruct online the PDD (Percentage Depth-Dose) distribution of a proton beam (30 MeV and 150 MeV) with both conventional and high- intensity.



60 new generation SiC (sensitive area of 15 x 15 mm<sup>2</sup> and active thickness of 10.3  $\mu\text{m}$ ) in a stack configuration.

# Silicon Carbide

---

# Principal properties at room temperature of 4H-SiC compared to Silicon and Diamond

Properties	Diamond	Silicon	4H-Silicon Carbide
Energy Gap [eV]	5.45	1.12	3.26
Hole lifetime $\tau_p$	$10^{-9}$	$2.5 \cdot 10^{-3}$	$6 \cdot 10^{-7}$
Relative dielectric constant $\epsilon_r$	5.7	11.9	9.7
e-h pair energy (eV)	13	3.62	7.78
Density (gr/cm <sup>3</sup> )	3.52	2.33	3.21
Thermal conductivity (W/cm °C)	20	1.5	3-5
Electron mobility [cm <sup>2</sup> /Vs]	1800-2200	1400-1500	800-1000
Hole mobility [cm <sup>2</sup> /Vs]	1200-1600	450-600	100-115
Breakdown electric field (MV/cm)	10	0.2-0.3	2.2-4.0
Max working temperature (°C)	1100	300	1240
Displacement [eV]	43	13-20	25

**Wide bandgap**  
lower leakage current than silicon

**High signal**  
Diamond 16 e/um  
SiC 51 e/um  
Si 89 e/um

=> more charge than diamond

**Fast response time**

**High Radiation hardness**

Disadvantages diamond production:

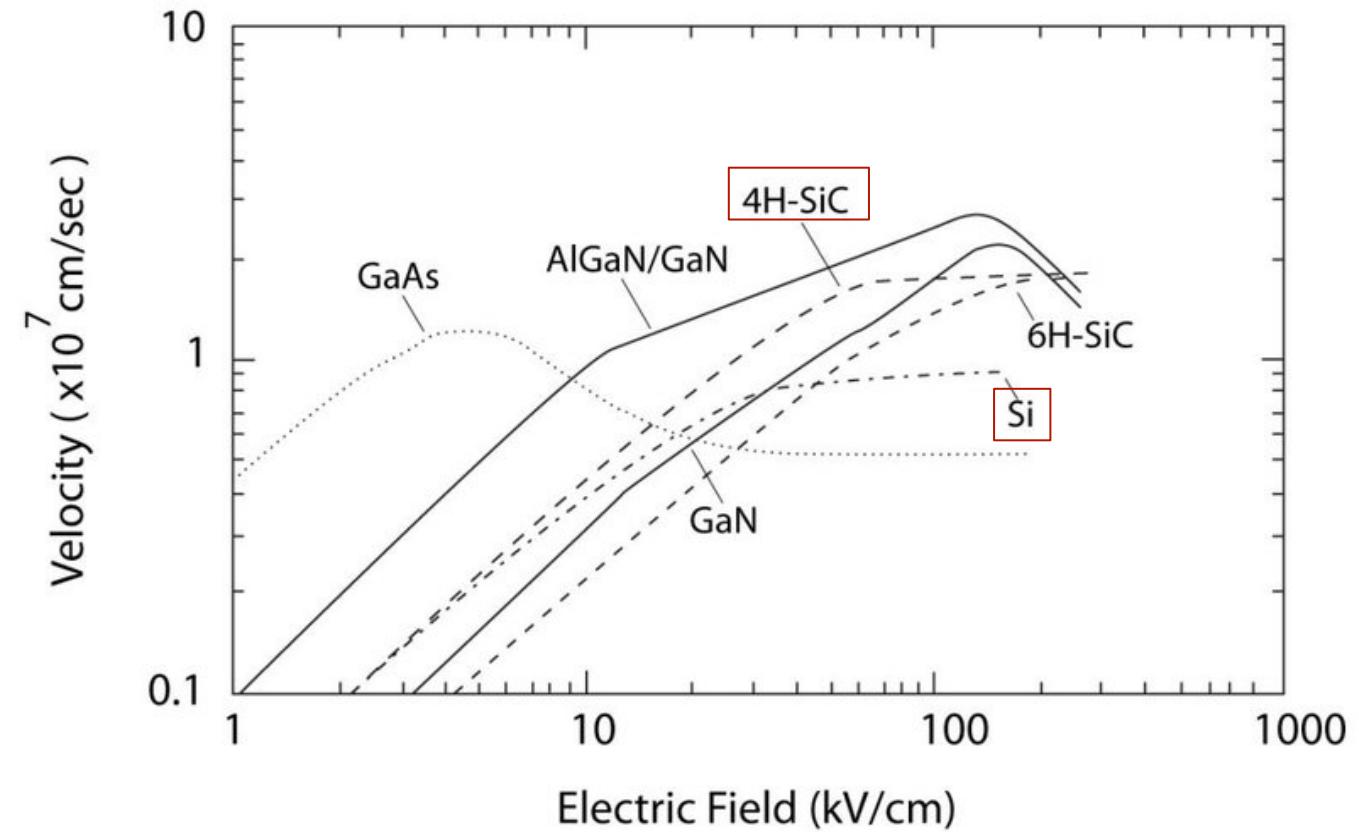
- higher costs;
- limited size while maintaining a high level of purity.

Main SiC Detectors features:

- dose rate independent
- LET independent
- linear response with absorbed dose
- high radiation hardness
- fast response

# Principal properties at room temperature of 4H-SiC compared to Silicon and Diamond

Saturated electron velocity [cm/s]	
Si	H4-SiC
$1 \times 10^7$	$2 \times 10^7$

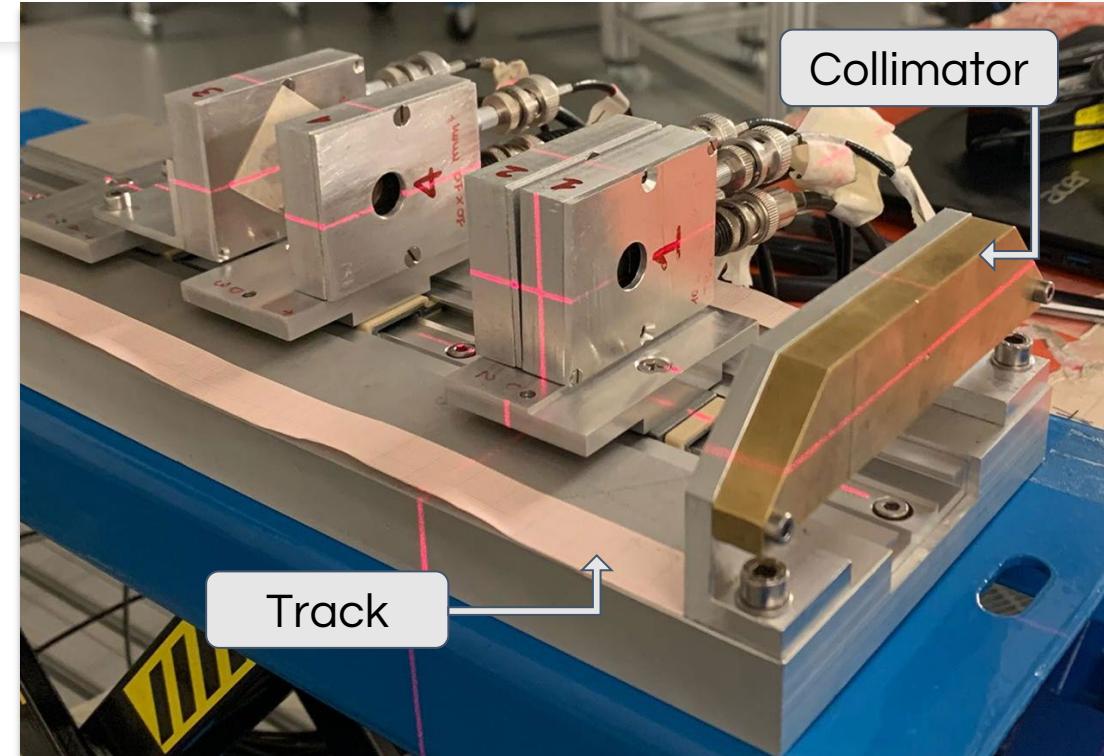
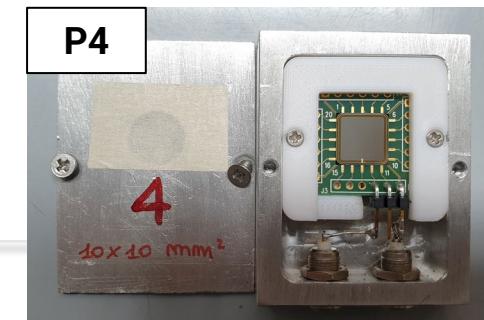
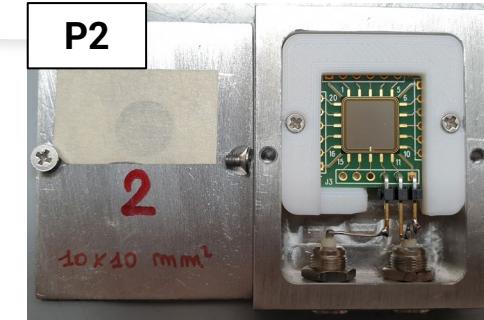
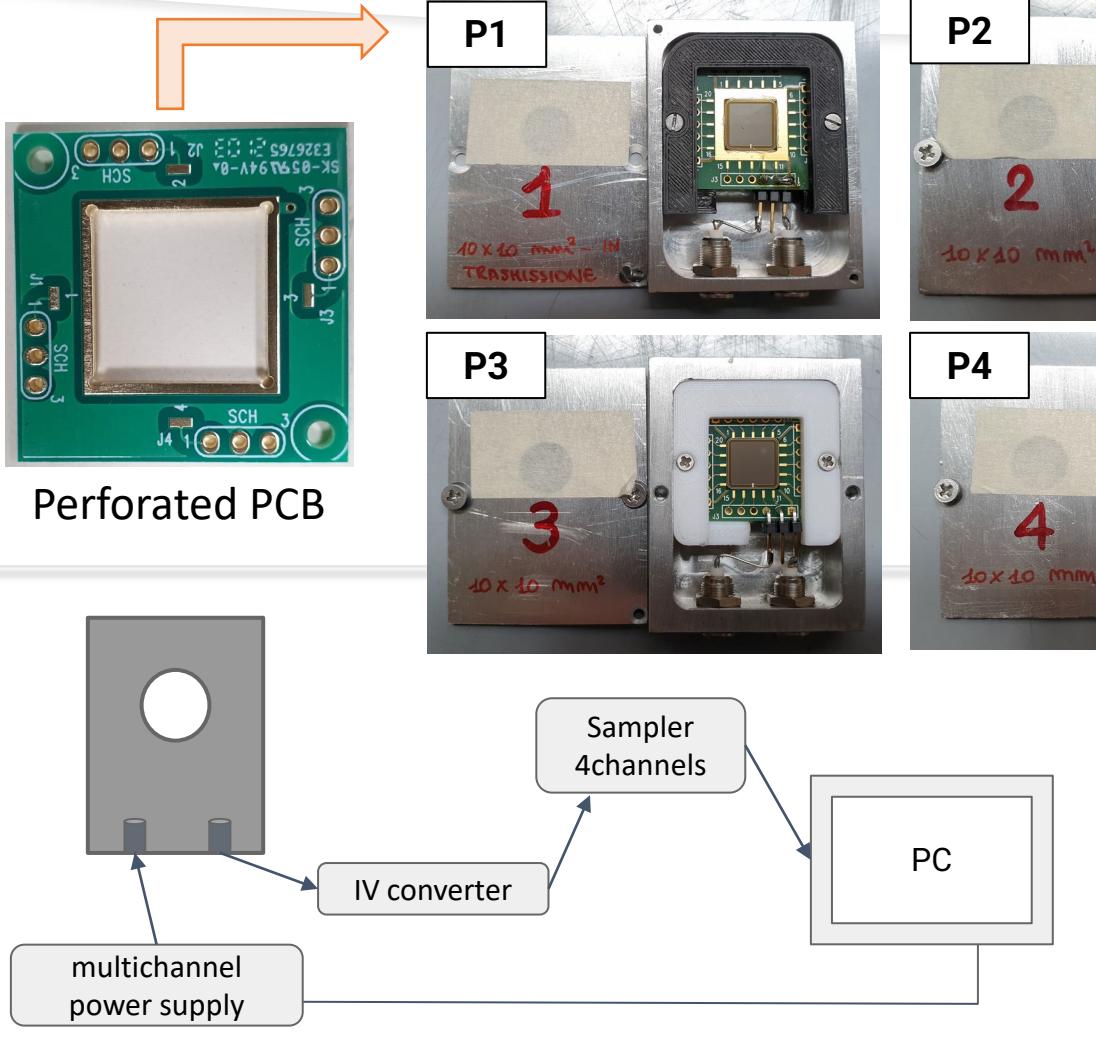


# PRAGUE prototype characterization

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# PRAGUE

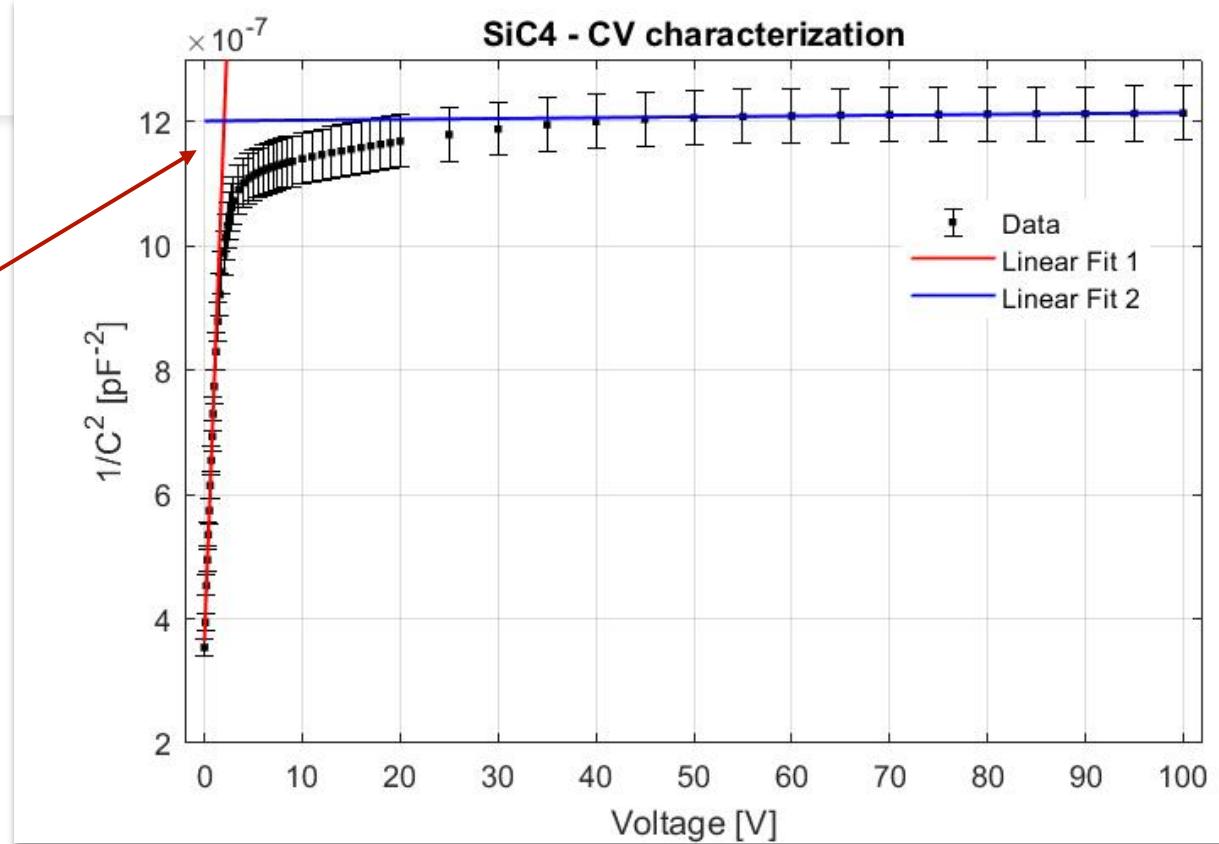
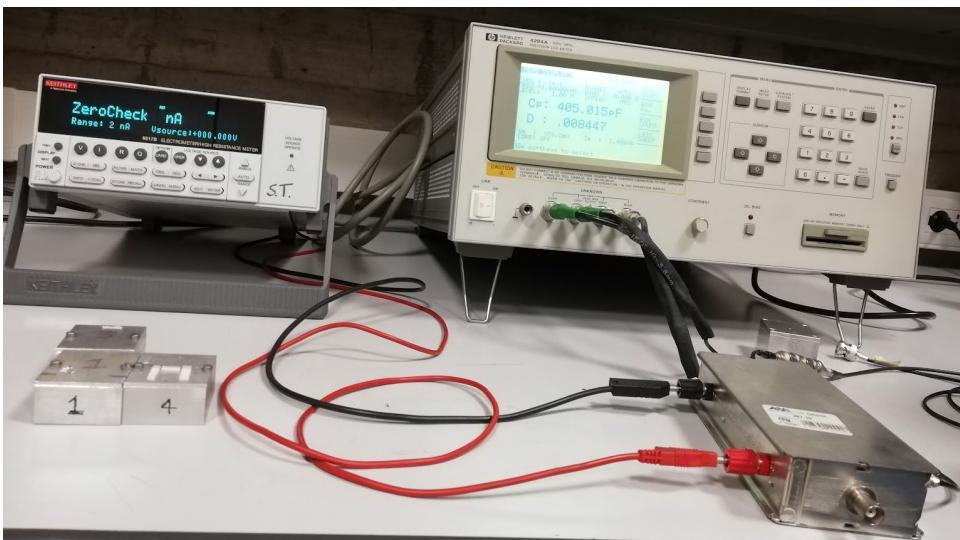
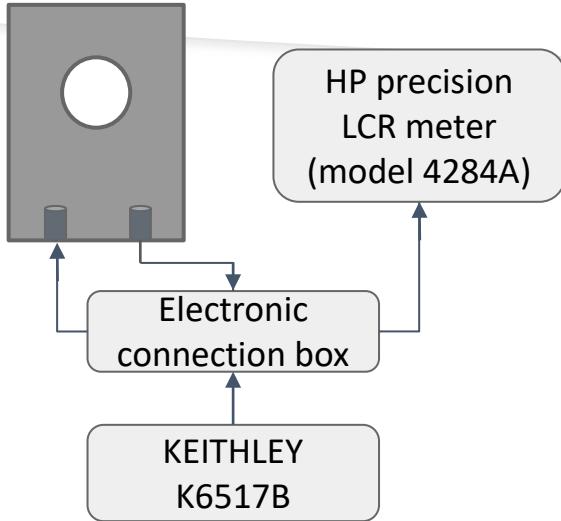
## The realization of a prototype made of 4 SiC detectors



Aluminum boxes contain a  $1 \times 1 \text{ cm}^2$  detector

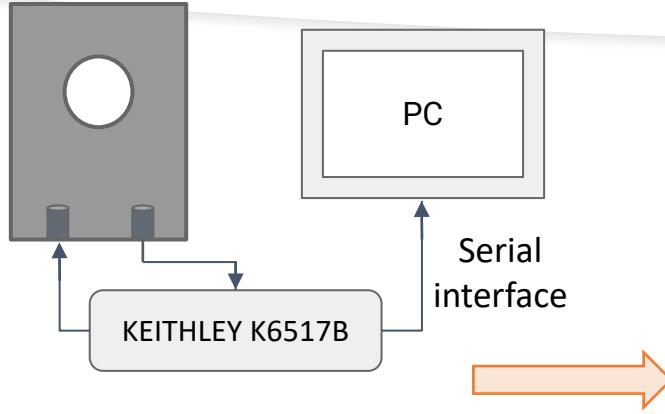
- active layer of **10  $\mu\text{m}$**
- passive layer of **110  $\mu\text{m}$**
- mounted on **PCB**.

# PRAGUE prototype – CV characterization



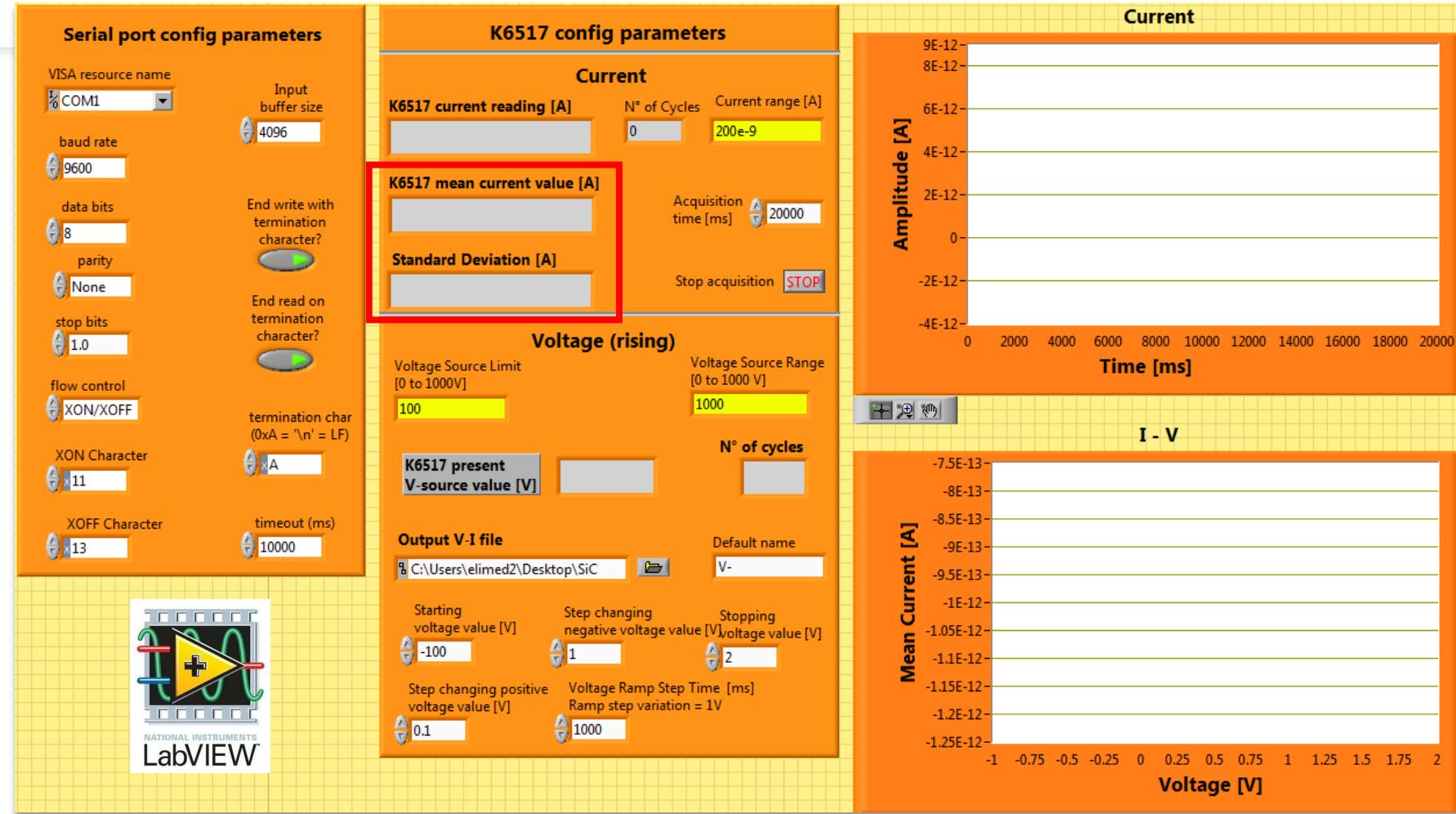
Depletion Voltage	SiC1	SiC2	SiC3	SiC4
	$1.8 \pm 0.5 \text{ V}$	$2.1 \pm 0.5 \text{ V}$	$1.9 \pm 0.5 \text{ V}$	$2.0 \pm 0.5 \text{ V}$
Saturation Capacitance	$923 \pm 16 \text{ pF}$	$895 \pm 16 \text{ pF}$	$896 \pm 16 \text{ pF}$	$908 \pm 16 \text{ pF}$

# PRAGUE prototype – IV characterization

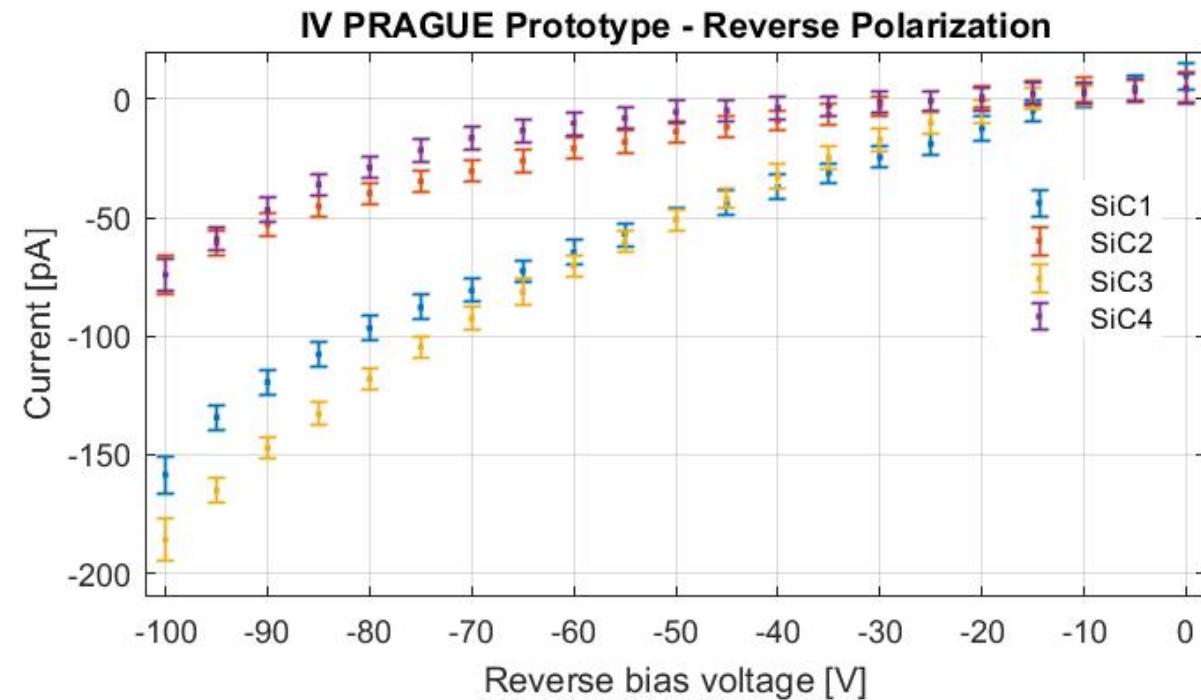
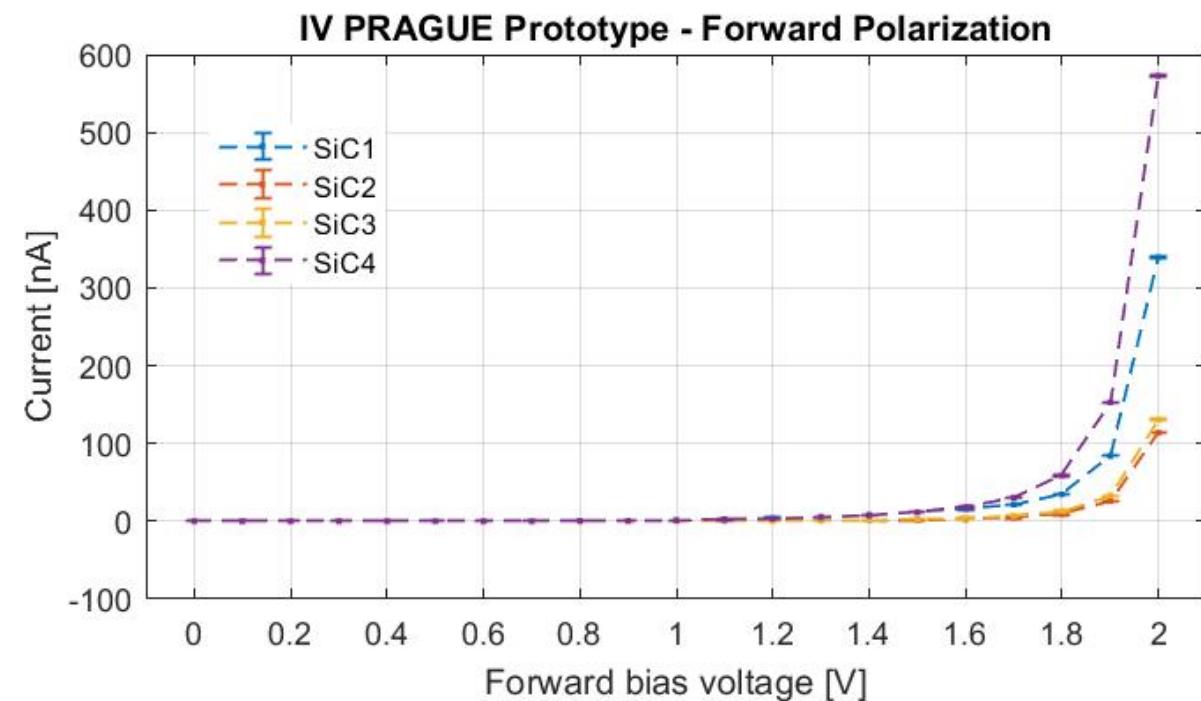
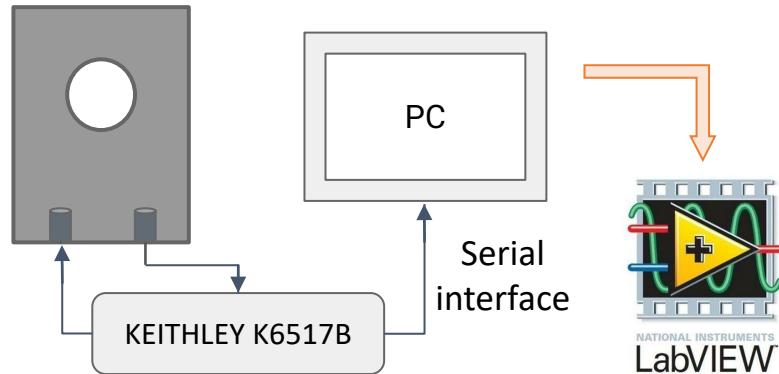
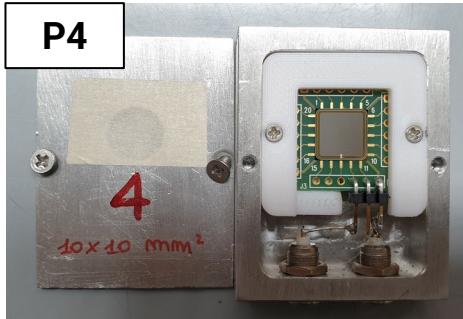
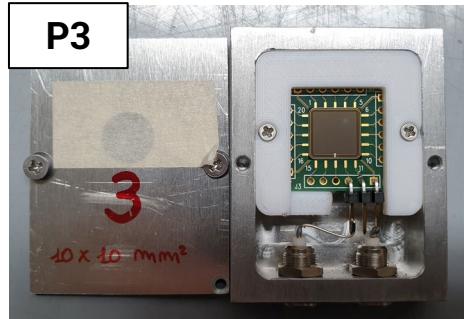
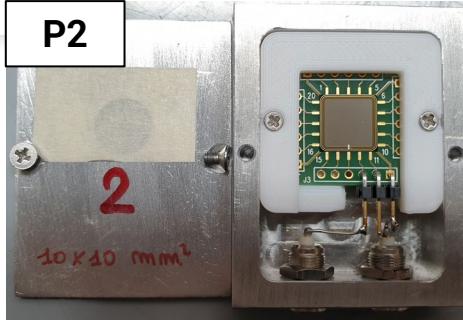


It is possible to set:

- **acquisition time** for current measurements;
- **current full scale**;
- **voltage ramp** (start and stop value, step voltage value, step voltage time);
- **voltage full scale**;
- **voltage limit**.



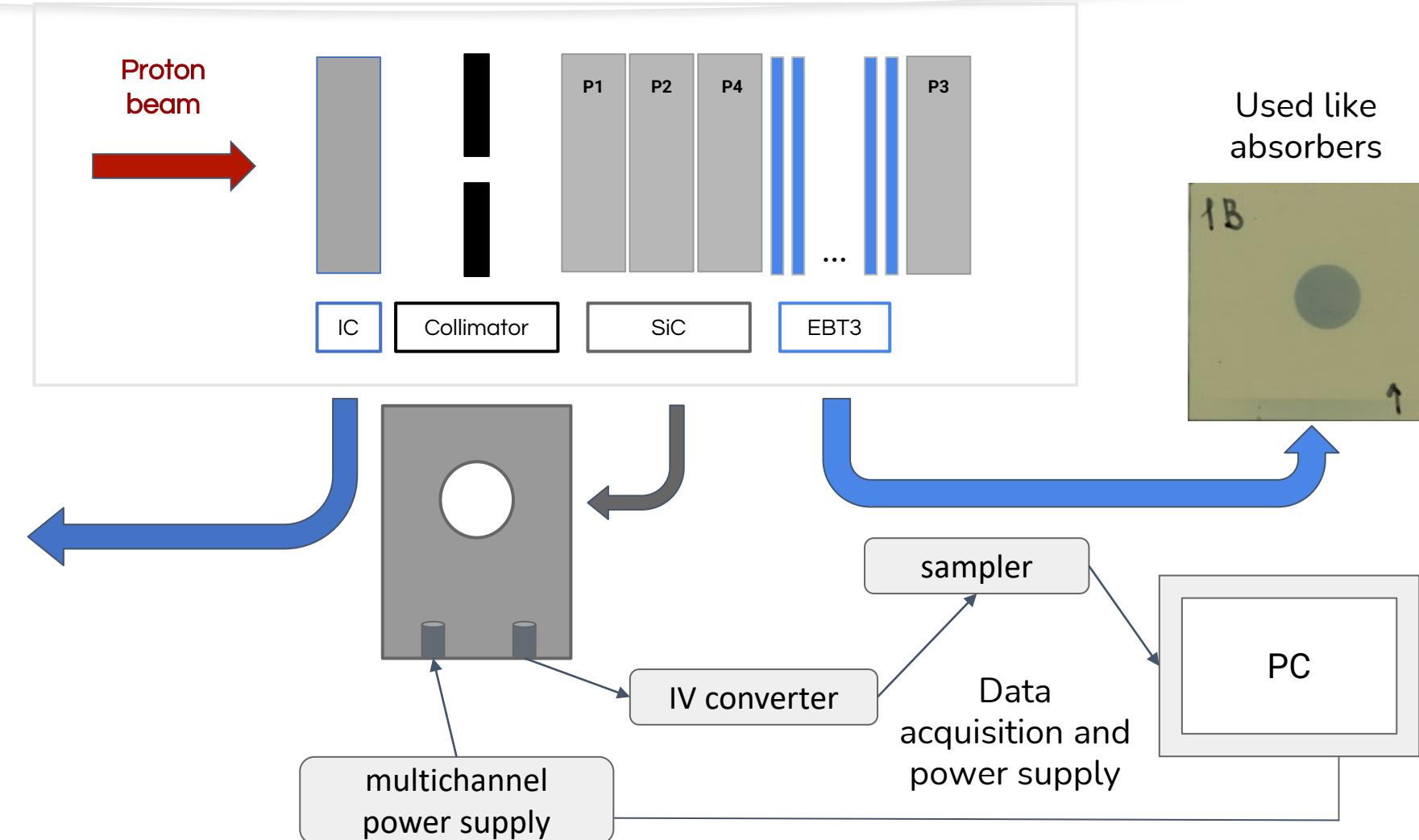
# PRAGUE prototype – IV characterization



# PRAGUE prototype - Experimental campain @Trento Proton Therapy Centre

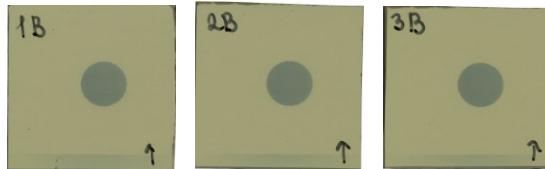


Ionization chamber provided by the center: it returns the number  $N$  of protons incident on the collimator and the dose  $D$  released at the isocenter.

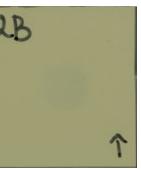
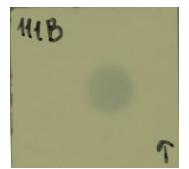
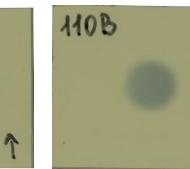
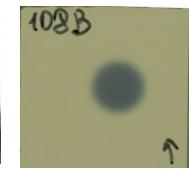


# PRAGUE Prototype

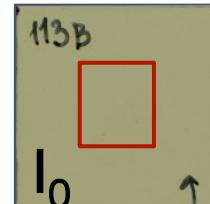
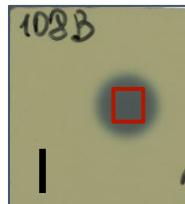
## A preliminary study @PTC of Trento - EBT3 data analysis



...



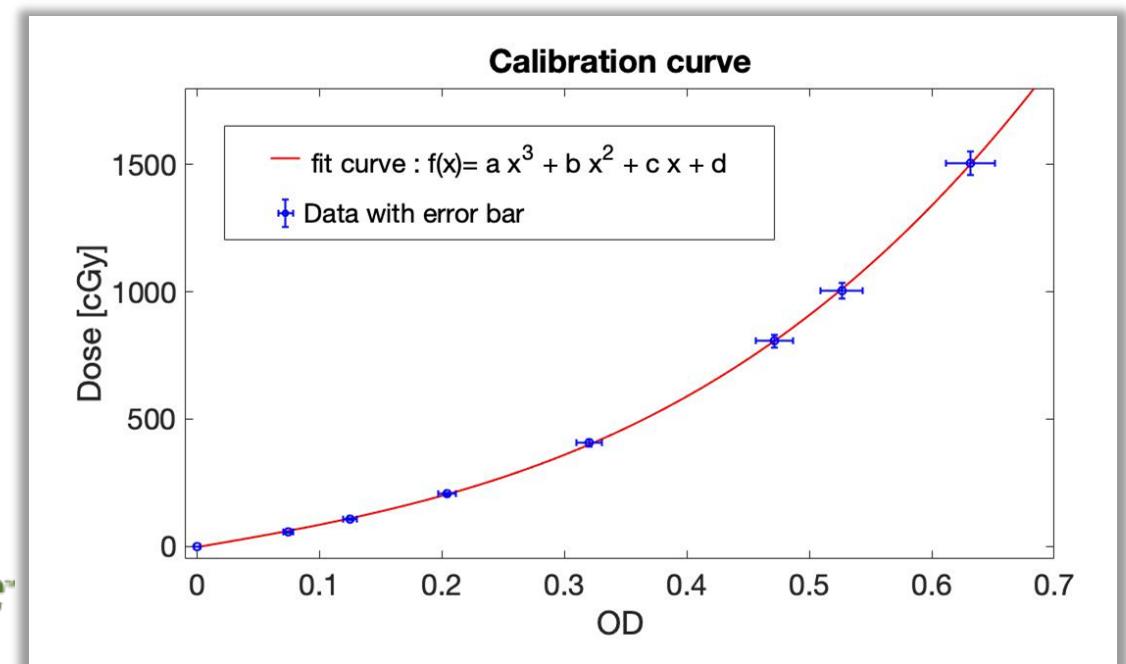
EBT3 stack  
irradiated with  
70 MeV proton  
beam.



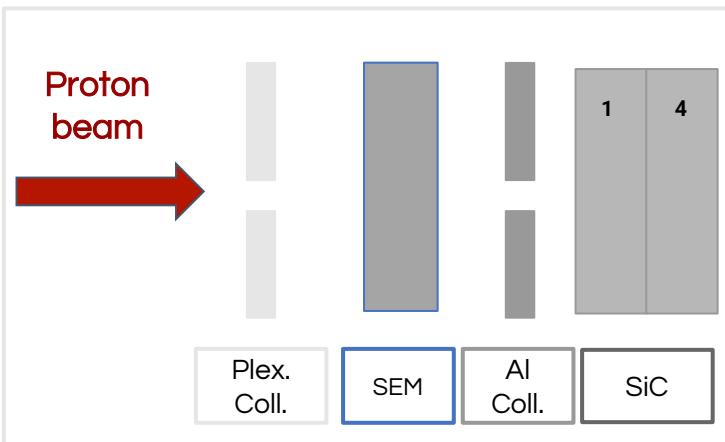
$$OD = -\log \frac{I}{I_0}$$

Property	EBT3	EBT3-U	HD-V2
Active layer thickness [ $\mu m$ ]	28	28	12
Passive layer thickness [ $\mu m$ ]	125	125	97
Number of passive layer	2	1	1
Dynamic dose range [Gy]	0.1-20	0.1-20	10-1000
Spatial resolution [ $\mu m$ ]	< 25	< 25	< 5
Water Equivalent Thickness [ $\mu m$ ]	$355 \pm 20$	$195 \pm 10$	$150 \pm 10$

To convert the OD film response in dose, the RCFs were  
firstly calibrated in terms of absorbed dose in water:



# PRAGUE Prototype @ Institute of Nuclear Physics Av Čr (CZ) - results



We acquired 10 shots of 10 s.  
Then we repeated the acquisition by inverting the detectors.

By comparing the answer of the detectors, I found that SIC1 and SIC4 at entrance read a mean current value of:

Detector	Mean current [nA]	Error [nA]
SIC 1	19,975	0,002
SIC 4	28,271	0,003

SIC4 reads more than SIC1 → we can find a factor k such that:

$$k = \text{SIC4}/\text{SIC1}$$

in other words:

$$\text{SIC4} = k \text{ SIC1}$$

or

$$\text{SIC1} = \text{SIC4}/k$$

k [a.u.]	Error [a.u.]
1,415	0,005

PDD distribution measurement:  
state of art

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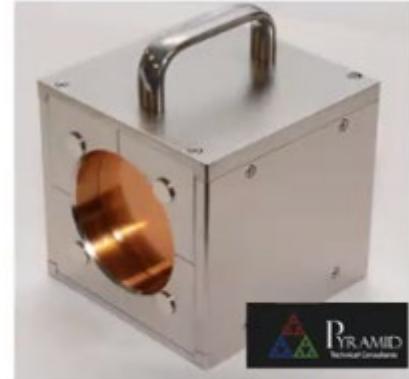
# State of art on PDD measurement in protontherapy



Water tank with a motorized system



Multi-layer Ionization Chambers



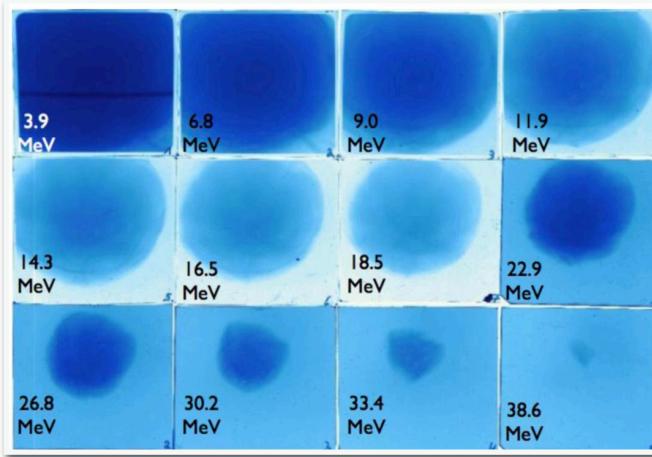
Multi Faraday Cups



Scintillator stack

Detector	Advantage	Disadvantage	Spatial resolution
Water Tank and ionization chamber	Linear response, LET and energy independent	dose rate dependent, high time consuming	~ 0.20 mm
MultiLayer Ionization Chamber	Linear response, LET and energy independent	dose rate dependent, low spatial resolution (order of mm)	~ 1 mm
Multi Layer Faradaycup	Linear response, LET and energy independent, dose rate independent	low spatial resolution (order of mm), high activation amount	~ 1 mm
Scintillator stack	High spatial resolution, linear response	LET and energy-dependent, low radiation hardness	~ 0.25 mm

# State of art on PDD measurement – laser driven beam



Radiochromic films

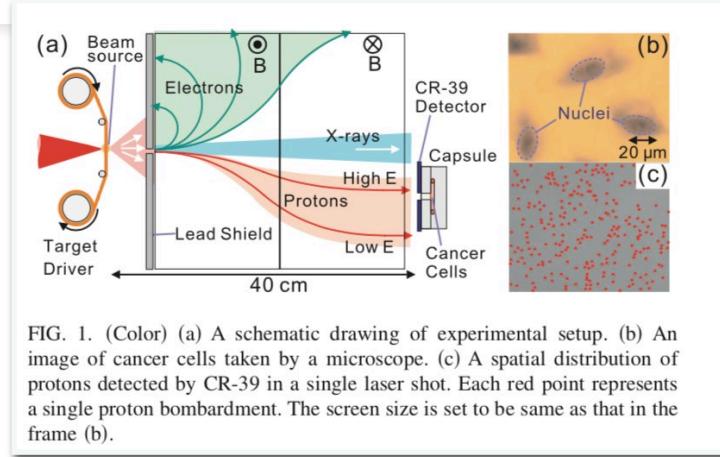
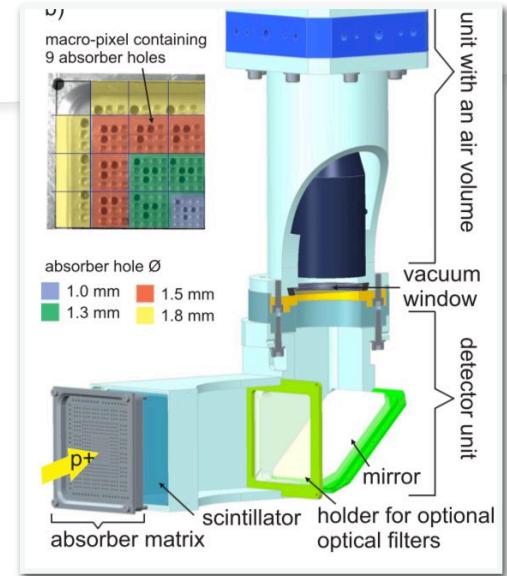


FIG. 1. (Color) (a) A schematic drawing of experimental setup. (b) An image of cancer cells taken by a microscope. (c) A spatial distribution of protons detected by CR-39 in a single laser shot. Each red point represents a single proton bombardment. The screen size is set to be same as that in the frame (b).

CR39 detector



Scintillator stack/grid

Detector	Advantage	Disadvantage
Radiochromic films	Linear response, dose rate independent	LET and energy-dependent, passive detector, high time consuming
CR39 detector	Linear response, dose rate independent	Saturation in fluency and incident energy, high time consuming
Scintillator systems	High spatial resolution, linear response	LET and energy-dependent, low radiation hardness

# What do we expect?

<b>Proton LASER Beam</b>					
	<b>Energy [MeV]</b>	<b>N° of particles</b>	<b>Charge [nC]</b>	<b>Shot time [ns]</b>	<b>Current</b>
<b>Maximum</b>	1	$10^7$	191,5	100	1,91 A
<b>Minimum</b>	60	$10^4$	0,006	100	57583,5 nA

<b>Proton Continuous Beam</b>					
	<b>Energy [MeV]</b>	<b>N° of particles</b>	<b>Charge [nC]</b>	<b>Shot time [s]</b>	<b>Current</b>
<b>Maximum</b>	1	$10^9$	19146,5	60	319,1 nA
<b>Minimum</b>	250	$10^4$	0,002	1	0,002 nA